NEARSIGHTEDNESS IN MATERIALS WITH INDIRECT BAND GAP

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Abstract. We investigate the nearsightedness property in the linear tight binding model at zero Fermi-temperature. We focus on the decay property of the density matrix for materials with indirect band gaps. By representing the density matrix in reciprocal space, we establish a qualitatively sharp estimate for the exponential decay rate in homogeneous systems. An extending result under perturbations is also derived. This work refines the estimates presented in (Ortner, Thomas & Chen 2020), particularly for systems with small band gaps.

1. INTRODUCTION

The electronic structure determines a wide range of physical and chemical properties of materials. For its computation, density functional theory (DFT) has been successfully applied for many decades [\[13,](#page-23-0) [23\]](#page-23-1). However, even in the minimalistic tight binding models, the practical implementations typically incur a high computational cost, scaling cubically with the system size. One approach to alleviate this high cost is through linear scaling algorithms [\[2,](#page-23-2) [15,](#page-23-3) [22,](#page-23-4) [25\]](#page-24-0), which rely on a notion of locality of electronic systems, often known as "nearsightedness".

First introduced by Kohn [\[22,](#page-23-4) [30\]](#page-24-1), nearsightedness describes the principle that interactions in many-atom systems are predominantly localised. Mathematically, this corresponds to the exponential off-diagonal decay of the density matrix. The decay rate determines the error committed when truncating it during a numerical simulation, constituting the foundation for developing linear scaling techniques in electronic structure calculations.

Therefore, exploring the dependence of the decay rate on various factors is important and has provoked extensive discussion, both analytically and numerically [\[1,](#page-23-5) [5,](#page-23-6) [14,](#page-23-7) [18,](#page-23-8) [27\]](#page-24-2): it is determined by the band gap in insulators and by the Fermi-temperature in metals. However, these results may not always be sufficiently precise to account for the exponential decay observed in some materials with small band gaps, such as semiconductors like silicon and germanium. Numerical results from [\[27\]](#page-24-2) show that in the silicon system, the decay is nearly identical to the carbon system while the former has a much smaller band gap.

The main purpose of this paper is to explore a subtle point that, to the best of our knowledge, has been missed in the nearsightedness discussion to date: the decay rate of the density matrix depends not on the *direct band gap* (the most common notion of a band gap) but on the *indirect* band gap; cf. Figures [1](#page-3-0) and [2.](#page-4-0)

Our main results establishes this, for the case of linear tight binding models at zero Fermitemperature, and show that this result is stable under perturbations.

This result is important because the indirect band gap can be much larger than the direct band gap, especially in small-gap semiconductors such as Mg_2Si ; cf. Figure [2.](#page-4-0) The result explains why some small gapped systems still exhibit excellent exponential localization and linear scaling methods remain applicable.

Next, we explore whether such improved locality estimates also generalize to the interatomic forces, which is called strong locality in [\[5,](#page-23-6) [26\]](#page-24-3). Through a combination of analytical and numerical empirical results we show that this is not the case. This negative result demonstrates that locality of interatomic forces is a fundamentally stronger concept than classical nearsightedness.

1.1. Outline. In Section 2, we introduce the physical background and linear tight binding models. We then provide definitions for the direct band gap gap[−] and indirect band gap gap⁺ in reciprocal space. In Section 3, we state the main results of this paper. To this end, we first

discuss the dependence of nearsightedness in homogeneous systems, and then extend the result to the inhomogeneous systems with bounded perturbations. The results show that the decay rate actually depends on gap₊, and perturbations introduce a slower decay controlled by gap and the norm of the perturbations. At the end of our analysis, we further explore the decay rate for the derivatives of the density matrix, showing it depends on gap−. In Section 4, we provide numerical experiments to verify our analytical results. The main conclusions of this paper are summarised in Section 5. All proofs are collected in Section 6. In the appendix, we provide details of the Bloch transform, along with the specifics of numerical experiments.

1.2. **Notation.** The symbol $\|\cdot\|$ and $|\cdot|$ will denote the ℓ^2 and Euclidean norms on \mathbb{R} or \mathbb{C} , respectively. The subscript of ∥ · ∥ indicates the norm is taken in which sense. In particular, we will use $\|\cdot\|_F$ to denote the Frobenius norm for matrices. The ball of radius R about ℓ and 0 will be denoted by $B_R(\ell)$ and B_R , respectively. For a shifted lattice, we will write $\Lambda - \ell := \{x - \ell : x \in \Lambda\}.$ For two sets A and B, we denote the Minkowski sum of them by $A + B := \{a + b \mid a \in A, b \in B\}$, which is formed by adding each vector in A and B. For a self-adjoint operator T, the spectrum of T will be denoted by $\sigma(T)$.

We will use \oint to denote contour integral and f to denote the average integral over its domain, that is,

$$
\int_{\Omega} := \frac{1}{|\Omega|} \int_{\Omega},
$$

where $|\Omega|$ is the volume of the integral domain Ω .

The symbol C is a positive generic constant that may vary between successive lines of estimation. When estimating rates of decay, C consistently remains independent of the system size and lattice position. The dependencies of C will be typically evident from the context or explicitly stated. For simplicity, we sometimes write $f \lesssim g$ to mean $f \leq Cg$ for certain generic positive constant as above.

2. Tight Binding Models

2.1. Atomistic Model and Admissible Configurations. We begin with a homogeneous multi-lattice Λ defined as follows: Let $A\mathbb{Z}^d$ be a Bravais lattice (where A is non-singular and d is the dimension of the system) and $\{p_i\}_{i=1}^M \subset \mathbb{R}^d$ be a set of M shift vectors. Then, we define

$$
\Lambda := \bigcup_{i=1}^{M} \left(p_i + \mathsf{A} \mathbb{Z}^d \right) \tag{2.1}
$$

which is formed by taking the union of shifted Bravais lattice $A\mathbb{Z}^d$ along p_i , $i = 1, ..., M$. We denote by Γ a unit cell of $A\mathbb{Z}^d$ including M atoms, and by Γ^* the corresponding unit cell of the reciprocal lattice $2\pi A^{-T}\mathbb{Z}^d$. For example, we can simply take $\Gamma := A[-\frac{1}{2}]$ $\frac{1}{2}, \frac{1}{2}$ $(\frac{1}{2})^d$ and $\Gamma^* := 2\pi A^{-T}[-\frac{1}{2}]$ $\frac{1}{2}, \frac{1}{2}$ $(\frac{1}{2})^d$, but other choices are possible.

Following [\[5,](#page-23-6) [26,](#page-24-3) [27\]](#page-24-2), we consider displacements $u : \Lambda \to \mathbb{R}^d$ and thus configurations of the form $(\ell + u(\ell))_{\ell \in \Lambda}$. For brevity, we write

$$
\mathbf{r}_{\ell k}(u) := \ell + u(\ell) - k - u(k) \text{ and } r_{\ell k}(u) := |\mathbf{r}_{\ell k}(u)|.
$$
 (2.2)

When $u(\ell) = 0$ for all $\ell \in \Lambda$, we will omit u and take $r_{\ell k}$, $r_{\ell k}$ for the remainder of the paper. Let us define the finite difference of u (the strain) by

$$
D_{\rho}u(\ell) := u(\ell + \rho) - u(\ell), \quad \forall \ell \in \Lambda, \ \rho \in \Lambda - \ell.
$$
 (2.3)

The infinite difference stencil is defined to be $Du(\ell) \coloneqq {D_{\rho}u(\ell)}_{\rho \in \Lambda - \ell}$, endowed with the norm

$$
||Du||_{\ell^2_{\Upsilon}} := \left(\sum_{\ell \in \Lambda} |Du(\ell)|^2_{\Upsilon}\right)^{1/2} \text{ with } |Du(\ell)|^2_{\Upsilon} := \sum_{\rho \in \Lambda - \ell} e^{-2\Upsilon|\rho|} |D_{\rho}u(\ell)|^2. \tag{2.4}
$$

Since all of the semi-norms $||D \cdot ||_{\ell^2_\Upsilon}$ for $\Upsilon > 0$ are equivalent [\[4\]](#page-23-9), we will fix $\Upsilon > 0$ for the remainder. We wish to consider the set of finite energy displacements with the following noninterpenetration condition:

$$
\text{Adm}(\Lambda) := \left\{ u : \Lambda \to \mathbb{R}^d \colon \|Du\|_{\ell^2_\Upsilon} < \infty, \ \exists \,\mathfrak{m} > 0 \text{ with } r_{\ell k}(u) \ge \mathfrak{m} \ \forall \ell, k \in \Lambda \right\}. \tag{2.5}
$$

2.2. Tight Binding Model. Let N_b denote the number of atomic orbitals per atom, indexed by $1 \leq a, b \leq N_b$. To each atomic site $\ell \in \Lambda$, we denote the atomic species by z_{ℓ} . For a given admissible configuration $u \in \text{Adm}(\Lambda)$, the state for the bond $(\ell, k) \in \Lambda \times \Lambda$ is defined by $\boldsymbol{x}_{\ell k}(u) = (\boldsymbol{r}_{\ell k}(u), z_{\ell}, z_k)$. For a function $f(\boldsymbol{x}_{\ell k})$ we write $\nabla f(\boldsymbol{x}_{\ell k}) := \nabla_{\boldsymbol{r}_{\ell k}} f((\boldsymbol{r}_{\ell k}, z_{\ell}, z_k))$.

The linear tight binding Hamiltonian is given by the following:

(TB) Suppose that the Hamiltonian takes the form of

$$
\mathcal{H}(u)_{\ell k}^{ab} = h^{ab}(\boldsymbol{x}_{\ell k}(u)) + \delta_{\ell k} \sum_{m \neq \ell} t^{ab}(\boldsymbol{x}_{\ell m}(u))
$$
\n(2.6)

for $\ell, k \in \Lambda$ and $1 \leq a, b \leq N_b$. The functions $h^{ab}, t^{ab} : (\mathbb{R}^d, \{z_\ell\}_{\ell \in \Lambda}, \{z_\ell\}_{\ell \in \Lambda}) \to \mathbb{R}$ are continuously differentiable with

$$
|h^{ab}(\boldsymbol{x}_{\ell k})| + |\nabla h^{ab}(\boldsymbol{x}_{\ell k})| \leq h_0 e^{-\gamma_0 r_{\ell k}} \quad \text{and}
$$

$$
|t^{ab}(\boldsymbol{x}_{\ell k})| + |\nabla t^{ab}(\boldsymbol{x}_{\ell k})| \leq h_0 e^{-\gamma_0 r_{\ell k}}
$$
 (2.7)

for some $h_0, \gamma_0 > 0$. Moreover, we assume that $h^{ab}((\mathbf{r}_{\ell k}(u), z_{\ell}, z_k)) = h^{ba}((-\mathbf{r}_{\ell k}(u), z_k, z_{\ell}))$.

In the following, we will denote by $\mathcal{H}^{\text{ref}} := \mathcal{H}(\mathbf{0})$ the reference Hamiltonian.

Remark 2.1. We note that the constants h_0, γ_0 in [\(2.7\)](#page-2-0) may be chosen to be independent of atomic species. Additionally, [\(2.7\)](#page-2-0) requires that the dependence of $\mathcal{H}(u)_{\ell k}^{ab}$ on site m decays exponentially in $r_{\ell m}(u) + r_{mk}(u)$. That is, we are assuming long-range Coulomb interactions are screened, a common assumption in many practical tight binding models [\[9,](#page-23-10) [24,](#page-23-11) [29\]](#page-24-4). We assume this to separate Coulomb type long-range range effects from those arising due to small band gaps.

Under the assumption (TB), we have $\sigma(\mathcal{H}(u)) \subset [\underline{\sigma}, \overline{\sigma}]$, where $\underline{\sigma}, \overline{\sigma}$ are real and only depend on d, $\mathfrak{m}, h_0, \gamma_0$, while independent of the system size. The detailed proof leveraging the Gershgorin circle theorem has been given in [\[5\]](#page-23-6).

The number of orbitals, $N_{\rm b}$, generally depends on the atom species and thus on the atom sites. Only for the sake of simplicity of notation we assume this number is the same for all species. This assumption is easily avoided; see [\[27\]](#page-24-2) for a possible approach. \Box

2.3. Direct and Indirect Band Gaps. Next, we review the concepts of direct and indirect band gaps. For this purpose, we first recall the Bloch transform, which provides a decomposition of \mathcal{H}^{ref} , denoted by \mathcal{H}_{ξ} for all $\xi \in \Gamma^*$. For more details, see Appendix [A.](#page-20-0) By applying an eigenvalue decomposition for \mathcal{H}_{ξ} , we can obtain energy band structure of the system and subsequently distinguish between direct and indirect band gaps.

$$
\left[\mathcal{H}_{\xi}\right]_{\ell_{0}k_{0}}^{ab} := \sum_{\alpha \in \mathbb{Z}^{d}} \left[\mathcal{H}^{\text{ref}}\right]_{\ell_{0}+\mathsf{A}\alpha,k_{0}}^{ab} e^{-i(\ell_{0}-k_{0}+\mathsf{A}\alpha)\cdot\xi} \quad \forall \xi \in \Gamma^{*},\tag{2.8}
$$

for all $\ell_0, k_0 \in \Lambda_0 := \Gamma \cap \Lambda, 1 \le a, b \le N_b$. The size of the matrix \mathcal{H}_{ξ} is $MN_b \times MN_b$. For $\ell \in \Lambda$, we write ℓ_0 for the unique site in Λ_0 satisfying $\ell - \ell_0 \in \mathsf{A}\mathbb{Z}^d$. Denoting the eigenvalues of \mathcal{H}_{ξ} by $\varepsilon_1(\xi) \leq \cdots \leq \varepsilon_{MN_{\rm b}}(\xi)$, we have

$$
\sigma(\mathcal{H}^{\text{ref}}) = \bigcup_{j=1}^{MN_{\text{b}}} \left\{ \varepsilon_{j}(\boldsymbol{\xi}) : \ \boldsymbol{\xi} \in \Gamma^{*} \right\},\tag{2.9}
$$

where $\varepsilon_j : \Gamma^* \to \mathbb{R}$ are referred to as the energy bands [\[20\]](#page-23-12).

We focus exclusively on systems with a positive band gap, such as insulators and semiconductors, where the Fermi level, ε_F , lies inside the band gap. The Fermi level ε_F separates the energy bands into the valence bands and conduction bands [\[10\]](#page-23-13); that is,

$$
\varepsilon_{\mathcal{F}} \notin \sigma(\mathcal{H}^{\text{ref}}) \quad \text{and} \quad \varepsilon_{N_0}(\xi) < \varepsilon_{\mathcal{F}} < \varepsilon_{N_0+1}(\xi) \quad \forall \xi \in \Gamma^*, \tag{2.10}
$$

for some N_0 , the total number of occupied states in the system.

In semiconductors, one can consider two types of band gaps: the direct gap gap[−] and the indirect gap gap_+ , defined respectively as

$$
\mathsf{gap}_{+} := \min_{\xi \in \Gamma^{*}} \big(\varepsilon_{N_{0}+1}(\xi) - \varepsilon_{N_{0}}(\xi)\big), \quad \text{and} \quad (2.11)
$$

$$
\mathsf{gap}_{-} \coloneqq \min_{\boldsymbol{\xi} \in \Gamma^*} \varepsilon_{N_0+1}(\boldsymbol{\xi}) - \max_{\boldsymbol{\xi} \in \Gamma^*} \varepsilon_{N_0}(\boldsymbol{\xi}). \tag{2.12}
$$

One can readily verify the following relation

$$
\mathsf{gap}_{+} = \min_{\boldsymbol{\xi} \in \Gamma^*} (\varepsilon_{N_0+1}(\boldsymbol{\xi}) - \varepsilon_{N_0}(\boldsymbol{\xi})) \geq \min_{\boldsymbol{\xi} \in \Gamma^*} \varepsilon_{N_0+1}(\boldsymbol{\xi}) - \max_{\boldsymbol{\xi} \in \Gamma^*} \varepsilon_{N_0}(\boldsymbol{\xi}) = \mathsf{gap}_{-}.
$$
 (2.13)

Notice that when $\text{gap}_- = \text{gap}_+$, the maximal energy of the valence bands and the minimal energy of the conduction bands occurs at the same vector $\xi \in \Gamma^*$, and the band gap will be referred to as a *direct band gap*. Conversely, if $\text{gap}_{+} > \text{gap}_{-}$, the two extrema occur at different ξ vectors, resulting in an *indirect band qap*. We exhibit the disparity by two schematic bands in the Figure [1,](#page-3-0) where we use the green strip and the orange bar to denote gap_- and gap_+ , respectively. In Figure [2,](#page-4-0) we present the band structure of Mg_2Si and C, with indirect band gaps. The calculation is performed using the DFTK.jl package [\[17\]](#page-23-14).

In physics, the disparity of direct and indirect band gaps leads to various properties of semiconductors, which are associated with electron-hole pair generation and certain optical effects. These effects depend on electronic transitions between the top of the valence bands and the bottom of the conduction bands [\[10,](#page-23-13) [20,](#page-23-12) [28\]](#page-24-5). Here, we investigate the role of the indirect band gap in the locality of electronic structure.

FIGURE 1. Schematic of the direct and indirect band gaps.

FIGURE 2. The band structure of Mg₂Si and C. In Carbon, we have gap_{\approx} gap_+ , whereas in Mg₂Si, we observe $\mathsf{gap}_- \ll \mathsf{gap}_+$.

3. Main Results

3.1. **Nearsightedness.** We now turn the attention to the *nearsightedness* property, which we sometimes call weak locality to distinguish it from locality of the mechanical response (strong locality). We first focus on the homogeneous lattice, and present an improved estimation for the locality of the density matrix, explicitly tracking the dependence on gap_{+} . Subsequently, we extend the analysis to include inhomogeneous cases with perturbations.

At zero Fermi-temperature, the Fermi-Dirac function is given by $\chi_{(-\infty,\varepsilon_{\mathrm{F}})}$ and thus the density matrix reads

$$
\rho(u) = \chi_{(-\infty,\varepsilon_F)}(\mathcal{H}(u)), \quad u \in \text{Adm}(\Lambda). \tag{3.1}
$$

For simplicity, we will denote by $\rho^{\text{ref}} := \rho(0)$, for which we have the following result:

Theorem 3.1. Suppose Λ has the form of [\(2.1\)](#page-1-0) and \mathcal{H}^{ref} satisfies (**TB**). Then, there exist constants $C_1, \eta_+ > 0$ such that

$$
\left|\rho_{\ell k, ab}^{\text{ref}}\right| \le \frac{C_1}{\text{gap}_+} e^{-\eta_+ r_{\ell k}}, \quad \forall \ell, k \in \Lambda, \ 1 \le a, b \le N_{\text{b}}, \tag{3.2}
$$

where $\eta_+ := c_1 \frac{\gamma_0}{h_0}$ $\frac{\gamma_0}{h_0} \min\left\{h_0, \gamma_0^d \textsf{gap}_+\right\}$ and $c_1, C_1 > 0$ only depend on d, $\mathfrak{m}, M, N_\text{b}$.

Remark 3.2. As we will see from the proof, one may conclude [\(3.2\)](#page-4-1) but with the prefactor C_1 $\frac{C_1}{\text{gap}_+}$ replaced with a constant multiple of $\left(\int_{\Gamma^{\star}}\left[\varepsilon_{N_0+1}(\boldsymbol{\xi})-\varepsilon_{N_0}(\boldsymbol{\xi})\right]^{-2}\mathrm{d}\boldsymbol{\xi}\right)^{1/2}$. □ □

Remark 3.3 (Existing results). We briefly note here that (3.2) but with gap₊ replaced with gap[−] is classical and follows from a contour integral representation of the electron density, together with existing Combes–Thomas type estimates on the resolvent [\[1,](#page-23-5) [5,](#page-23-6) [12,](#page-23-15) [14,](#page-23-7) [27\]](#page-24-2). That is, we let $\mathscr C$ be a simple, closed, positively oriented contour encircling $\sigma(\mathcal{H}^{\text{ref}}) \cap (-\infty, \varepsilon_F)$ (depicted in Figure [3\)](#page-5-0), write

$$
\rho^{\text{ref}} = \oint_{\mathscr{C}} \chi_{(-\infty,\varepsilon_{\text{F}})}(z) \left(z - \mathcal{H}^{\text{ref}}\right)^{-1} \frac{\mathrm{d}z}{2\pi i} = \oint_{\mathscr{C}} \left(z - \mathcal{H}^{\text{ref}}\right)^{-1} \frac{\mathrm{d}z}{2\pi i},\tag{3.3}
$$

and use the following Combes–Thomas estimate: for $\mathfrak{d}^{\text{ref}} := \text{dist}(z, \sigma(\mathcal{H}^{\text{ref}})) > 0$, we have

$$
\left| \left(z - \mathcal{H}^{\text{ref}} \right)_{\ell k}^{-1} \right| \le \frac{2}{\mathfrak{d}^{\text{ref}}} e^{-\gamma_{\text{CT}}(\mathfrak{d}^{\text{ref}}) r_{\ell k}} \tag{3.4}
$$

where $\gamma_{\text{CT}}(\mathfrak{d}^{\text{ref}}) = c_0 \frac{\gamma_0}{h_0}$ $\frac{\gamma_0}{h_0} \min\{h_0, \gamma_0^d \mathfrak{d}^{\text{ref}}\}\$ with $c_0 = c_0(d, \mathfrak{m})$ depending only on the geometry. □

Sketch of the Proof of Theorem [3.1.](#page-4-2) As in (3.3) , we consider a contour $\mathscr C$ separating the valence bands from the conduction bands, but now use the Bloch decomposition of the resolvent (see Appendix [A\)](#page-20-0), to write

$$
\rho_{\ell k,ab}^{\text{ref}} = \oint_{\mathscr{C}} \left[\oint_{\Gamma^*} (z - \mathcal{H}_{\xi})^{-1} e^{i\xi \cdot (\ell - k)} \mathrm{d}\xi \right]_{\ell_0 k_0, ab} \frac{\mathrm{d}z}{2\pi i}
$$
\n
$$
= \oint_{\Gamma^*} \left[\oint_{\mathscr{C} + \nu(\xi)} (z - \mathcal{H}_{\xi})^{-1} \frac{\mathrm{d}z}{2\pi i} \right]_{\ell_0 k_0, ab} e^{i\xi \cdot (\ell - k)} \mathrm{d}\xi
$$
\n
$$
= \oint_{\Gamma^*} \left[\hat{\rho}(\xi) \right]_{\ell_0 k_0, ab} e^{i\xi \cdot (\ell - k)} \mathrm{d}\xi, \tag{3.5}
$$

where $1 \le a, b \le N_b$, $\ell_0, k_0 \in \Lambda_0$ satisfy $\ell - \ell_0, k - k_0 \in \mathbb{A} \mathbb{Z}^d$, and $\nu : \Gamma^* \to \mathbb{C}$ satisfies $\varepsilon_{N_0}(\boldsymbol{\xi}) < \varepsilon_{\mathrm{F}} + \nu(\boldsymbol{\xi}) < \varepsilon_{N_0+1}(\boldsymbol{\xi}).$

We conclude by showing that ν and thus $\hat{\rho}$ extend to analytic functions on a strip of width proportional to gap_{+} and then apply a suitable Paley–Wigner estimate. For full details, see Section [6.1.](#page-12-0) \Box

We now show that the previous locality result is stable under perturbations. Specifically, we extend the result to inhomogeneous systems with finite-energy displacements of the lattice. Since those perturbations must have finite energy-norm, they are necessarily localized, but with relatively slow (e.g., algebraic) decay.

Theorem 3.4 (Local Perturbations). Suppose $u \in \text{Adm}(\Lambda)$ and $\mathcal{H}(u)$ satisfies (TB) with $\varepsilon_F \notin \sigma(H(u))$. Then, there exist positive constants $C_1, C_{\ell k}(u), \eta_+$ and η_- such that

$$
|\rho(u)_{\ell k, ab}| \le \frac{C_1}{\text{gap}_+} e^{-\eta_+ r_{\ell k}} + C_{\ell k}(u) e^{-\eta_- r_{\ell k}},
$$
\n(3.6)

for all $\ell, k \in \Lambda$ and $1 \le a, b \le N_b$. Here, C_1, η_+ are defined in Theorem [3.1,](#page-4-2) and $\eta_- :=$ $c_0\min\{h_0,\gamma_0^d$ gap $_\}$ for some $c_0>0$ depending only on d, \mathfrak{m},h_0 and $\gamma_0.$ Moreover, for sufficiently large $R' > 0$,

$$
C_{\ell k}(u) := C(u) \left(\|Du\|_{\ell^2_{\Upsilon}(\Lambda \setminus B_{R'})} + e^{-2\eta_{-} \min_{m \in B_{R'}} (r_{\ell m} + r_{mk})} \right) \tag{3.7}
$$

where $C(u) := \frac{C_2 ||Du||_{\ell^2_{\Upsilon}}}{\text{gap}_{-}} \left(1 + \frac{R^d e^{4\eta - R}}{\text{gap}_{-}^2}\right)$ $\frac{R^de^{4n}}{4R^{2d+4}}$ with $C_2 > 0$ depending on $h_0, \gamma_0, \mathfrak{m}, d, N_{\mathrm{b}}, M$, and $R > 0$ 0 satisfying $||Du||_{\ell^2_\Upsilon(\Lambda\setminus B_R)} \leq C_3$ gap₋ for some $C_3 > 0$. In particular, for sufficiently small $||Du||_{\ell^2_\Upsilon}$, R and R' can be chosen arbitrarily.

FIGURE 3. A schematic plot of the contour $\mathscr C$ circling the whole spectrum of valence bands denoted by the green strip, and the conduction bands denoted in blue.

Remark 3.5. If $|Du(\ell)|_T \lesssim (1+|\ell|)^{-\alpha}$ for some $\alpha > d$, we can take \mathscr{C} in [\(3.8\)](#page-6-0) satisfying $dist(\mathscr{C}, \sigma(\mathcal{H}^{\text{ref}})) \geq \frac{1}{2}$ $\frac{1}{2}$ gap₋, and then obtain a simpler prefactor $C(u)$ of the form depending on $\|Du\|_{\ell^2_\Upsilon}$ and $\mathsf{gap}_$. □

Sketch of the Proof. We separate $|\rho(u)_{\ell k,ab}|$ into two parts by the triangle inequality,

$$
|\rho(u)_{\ell k,ab}| \leq \left|\rho^{\text{ref}}_{\ell k,ab}\right| + \left|\rho(u)_{\ell k,ab} - \rho^{\text{ref}}_{\ell k,ab}\right|.
$$

Notice that the first term on the right hand side has already been provided by Theorem [3.1,](#page-4-2) so we only need to consider the second term, which can be written as

$$
\left|\rho(u)_{\ell k,ab} - \rho_{\ell k,ab}^{\text{ref}}\right| = \left|\oint_{\mathscr{C}} \left[\left(z - \mathcal{H}(u)\right)^{-1} \left(\mathcal{H}(u) - \mathcal{H}^{\text{ref}}\right) \left(z - \mathcal{H}^{\text{ref}}\right)^{-1} \right]_{\ell k,ab} \frac{\mathrm{d}z}{2\pi i}\right|.
$$
 (3.8)

For the reference resolvent, we apply the Combes–Thomas estimate [\(3.4\)](#page-4-4). By approximating $\mathcal{H}(u)$ with a finite rank update of \mathcal{H}^{ref} , we are able to extend [\(3.4\)](#page-4-4) as:

$$
\left| \left(z - \mathcal{H}(u) \right)^{-1}_{\ell k, ab} \right| \leq \frac{4}{\mathfrak{d}^{\text{ref}}} e^{-\gamma_{\text{CT}}\left(\frac{1}{2} \mathfrak{d}^{\text{ref}} \right) r_{\ell k}} + C(u) e^{-\frac{1}{2}\gamma_{\text{CT}}\left(\frac{1}{2} \mathfrak{d}^{\text{ref}} \right) \left(\left| \ell \right| + \left| k \right| \right)},
$$

where $\mathfrak{d}^{\text{ref}} \coloneqq \text{dist}\big(z, \sigma(\mathcal{H}^{\text{ref}})\big) > 0, \, \gamma_{\text{CT}}(\frac{1}{2})$ $\frac{1}{2}$ $\mathfrak{d}^{\text{ref}}$) is defined as in Remark [3.3,](#page-4-5) and $C(u)$ depends on $||Du||_{\ell^2_{\Upsilon}}$ and $\mathfrak{d}(u)$. By choosing \mathscr{C} such that dist $(\mathscr{C}, \sigma(\mathcal{H}^{\text{ref}})) \geq \frac{1}{2}$ $\frac{1}{2}$ gap₋, we can achieve the constant η_- in the above estimate. For full details, see Section [6.2.](#page-14-0)

Remark 3.6. The perturbation introduces a site-dependent constant $C_{\ell k}(u)$, which can be arbitrarily small as $|\ell|, |k| \to \infty$. That is, as ℓ, k move far away from the perturbation, the estimate in [\(3.6\)](#page-5-1) will be independent of the lattice sites. Moreover, as $||Du||_{\ell^2_T} \to 0$, the estimate converges to the homogeneous case in Theorem [3.1.](#page-4-2) Here we also note that the exponent η will be determined by $\mathsf{gap}_\mathsf{when}$ the system has a relatively small band gap. \Box

Remark 3.7. Analogously, we can also consider small global displacements u in the sense that the max-norm,

$$
||Du||_{\ell_{\infty}} := \sup_{\ell \in \Lambda} \sup_{\rho \in \Lambda - \ell} \frac{|D_{\rho}u(\ell)|}{|\rho|},
$$

is sufficiently small [\[6,](#page-23-16) [27\]](#page-24-2). The additional term in [\(3.6\)](#page-5-1) can be replaced by a site-independent estimate $C(u)e^{-\eta-r_{\ell k}}$ for some constant $C(u) > 0$ depending on $||Du||_{\ell_{\infty}}$ and $\mathfrak{d}(u)$.

Remark 3.8. More generally, we suppose $O : \mathbb{R} \to \mathbb{R}$ is a function that extends analytically to an open neighbourhood of the contour \mathscr{C} . Then, one can define the corresponding local quantities for all $\ell \in \Lambda$ by

$$
O_{\ell}(u) := \sum_{a=1}^{N_{\rm b}} \oint_{\mathscr{C}} O(z) \big(z - \mathcal{H}(u)\big)_{\ell \ell, a a}^{-1} \frac{dz}{2\pi i}.
$$
 (3.9)

Then, the observable corresponding to O is given by $\sum_{\ell} O_{\ell}(u) := \text{Tr}(O(\mathcal{H}(u)))$. All of our results can be extended to a general case in the similar manner, which also improve the results of $[5, 27]$ $[5, 27]$.

3.2. Strong Locality. The nearsightedness in density matrix is insufficient when we aim to understand locality of interatomic interaction, e.g. to study the construction of interatomic potential models or multi-scale schemes such as QM/MM coupling methods [\[3,](#page-23-17) [5,](#page-23-6) [6,](#page-23-16) [7,](#page-23-18) [11\]](#page-23-19), which involve choosing cut-off radius for the interaction. In such cases, the strong locality is required for justification.

The goal of this section is to determine the dependence of strong locality, by providing a sharp estimate of the derivative of the density matrix. In what follows, we will discuss in homogeneous and perturbed systems as before. Since the essence of both is not significantly different, we present the combined results in the following proposition. The outcome of this

analysis is that $\text{gap}_+ \gg \text{gap}_-$ does not appear to qualitatively improve the strong locality over previous results. The proof does not give new insights over previous results such as [\[5,](#page-23-6) [33\]](#page-24-6) and is therefore postponed to Section [6.3.](#page-18-0) Instead, we provide a heuristic argument in Remark [3.10](#page-7-0) why no better result can be expected. Our numerical experiments provide additional empirical support.

Proposition 3.9 (Locality of the Derivative). Suppose $u \in \text{Adm}(\Lambda)$ and $\mathcal{H}(u)$ satisfies (TB) with $\varepsilon_F \notin \sigma(\mathcal{H}(u))$. Then, for $1 \leq i_1 \leq d$, there exist positive constants $C_q(\text{gap}_-, C(u))$ and η ₋ such that

$$
\left|\frac{\partial[\rho(u)]_{\ell\ell,ab}}{\partial[u(k)]_{i_1}}\right| \le \left[\frac{C_q(\text{gap}_-)}{(1+r_{\ell k})^q} + C(u)\right]^2 e^{-2\eta - r_{\ell k}},\tag{3.10}
$$

for all $\ell \neq k, \ell, k \in \Lambda$ and $1 \leq a, b \leq N_b$. Here, η_- is defined in Theorem [3.4,](#page-5-2) and $C_q(\textsf{gap}_-) := cq! \frac{\textsf{gap}_-^q-1}{\textsf{gap}_+^q+(\textsf{gap}_-)}$ $\frac{q}{\text{gap}^{-1}(\text{gap}-1)}$ for some constant $c > 0$ only depending on $d, \mathfrak{m}, h_0, \gamma_0, N_{\text{b}}, M,$ and $C(u)$ depends on $||Du||_{\ell^2_{\Upsilon}}$ and $\mathfrak{d}(u)$.

Remark 3.10. Here, we argue that one may not improve (3.10) by replacing the exponent with a constant depending instead on gap_{+} . First, we note that

$$
\frac{\partial \rho_{\ell\ell,ab}}{\partial [\mathbf{r}_k]_j} := \frac{\partial [\rho(u)]_{\ell\ell,ab}}{\partial [u(k)]_j} \Big|_{u=0}
$$
\n
$$
= \oint_{\mathscr{C}} \left[\left(z - \mathcal{H}(u) \right)^{-1} \frac{\partial \mathcal{H}(u)}{\partial [u(k)]_i} \left(z - \mathcal{H}(u) \right)^{-1} \right]_{\ell\ell,ab} \frac{dz}{2\pi i}
$$
\n
$$
= \sum_{mn,a'b'} \frac{\partial \mathcal{H}_{mn}^{a'b'}}{\partial [\mathbf{r}_k]_i} \oint_{(\Gamma^\star)^2} \left[\oint_{\mathscr{C}} \left(z - \mathcal{H}_\xi \right)^{-1}_{\ell_0 m_0,aa'} \left(z - \mathcal{H}_\xi \right)^{-1}_{n_0 \ell_0,b'b} \frac{dz}{2\pi i} \right] e^{i\xi \cdot (\ell - m)} e^{i\zeta \cdot (n-\ell)} d\xi d\zeta.
$$
\n(3.11)

Therefore, as in the proof of Theorem [3.1,](#page-4-2) one may obtain the strong locality estimate from the locality of the Hamiltonian, as in (TB), and the analyticity of the functions

$$
(\xi,\zeta) \mapsto \oint_{\mathscr{C}} \left(z - \mathcal{H}_{\xi} \right)^{-1}_{\ell_0 m_0, a a'} \left(z - \mathcal{H}_{\zeta} \right)^{-1}_{n_0 \ell_0, b' b} \frac{\mathrm{d} z}{2 \pi i}.
$$
 (3.12)

Recall that in the analogous function $\hat{\rho}(\xi)$ [\(3.5\)](#page-5-3) for the nearsightedness estimate, one may extend the region of analyticity of $\hat{\rho}$ to a strip of width proportional to gap_{+} by replacing $\mathscr C$ with a contour depending on ξ .

However, this is not the case for the functions [\(3.12\)](#page-7-2). Since the contour $\mathscr{C} = \mathscr{C}(\xi, \zeta)$ must separate $\bigcup_{n\leq N_0} \big\{ \varepsilon_n(\xi) \big\}$ from $\bigcup_{n\geq N_0+1} \big\{ \varepsilon_n(\zeta) \big\}$ and separate $\bigcup_{n\leq N_0} \big\{ \varepsilon_n(\zeta) \big\}$ from $\bigcup_{n\geq N_0+1} \big\{ \varepsilon_n(\xi) \big\}$, the region of analyticity of (3.12) is a subset of

$$
\left\{ (\xi_1, \xi_2) \in (\mathbb{C}^d)^2 \colon \varepsilon_n(\xi_l) \neq \varepsilon_m(\xi_{l'}) \text{ for all } n \leq N_0 < m \text{ and } l, l' = 1, 2 \right\}. \tag{3.13}
$$

This region depends on gap_−.

In §[4,](#page-7-3) we give numerical experiments in which strongly suggest that the strong locality does indeed depend on gap_{-} rather than gap_{+} .

4. Numerical Experiments

4.1. **1D Toy Model.** In this section, we present numerical experiments to support our analytical results. We construct a 1D chain with controllable band structure, which allows us to adjust gap_+ and gap_- .

Let us consider an infinite 1D chain $\Lambda := \mathbb{Z}$. We construct the tight binding Hamiltonian $\mathcal{H}(u)$ by assigning each atom with two atomic orbitals. Only nearest-neighbour interactions are included. For the on-site block of the Hamiltonian matrix, we take a constant diagonal matrix with parameters c_1 and c_2 ; while the off-diagonal block is given by a linear function with a Gaussian envelope:

$$
\mathcal{H}(u)_{\ell\ell} = \begin{pmatrix} c_1 & 0 \\ 0 & c_2 \end{pmatrix} \quad \text{and} \quad \mathcal{H}(u)_{\ell k} = \begin{pmatrix} f_1(r_{\ell k}(u)) & f_3(r_{\ell k}(u)) \\ f_3(r_{\ell k}(u)) & f_2(r_{\ell k}(u)) \end{pmatrix} \quad k \neq \ell,\tag{4.1}
$$

where the hopping functions $f_i(r) = (b_i r + a_i)e^{-d_i r^2}$ with parameters $a_i, b_i, d_i, i = 1, 2, 3$. One can verify that $\mathcal{H}(u)$ satisfies the assumption (TB). Applying the Bloch transform for $\mathcal{H}(0)$ gives

$$
\mathcal{H}_{\xi} = \begin{pmatrix} c_1 + 2f_1(1)\cos(\xi) & 2f_3(1)\cos(\xi) \\ 2f_3(1)\cos(\xi) & c_2 + 2f_2(1)\cos(\xi) \end{pmatrix}, \qquad \forall \xi \in \Gamma^* = [-\pi, \pi]. \tag{4.2}
$$

By solving the eigenvalue problem $\mathcal{H}_{\xi}u_n(\xi) = \varepsilon_n(\xi)u_n(\xi)$, we will obtain two energy bands ${\{\varepsilon_n(\xi)\}}_{n=1,2}$, as well as an analytic expression for gap_+ , which makes it possible for us to build a chain with different gap_- but a roughly fixed gap_+ ; cf. the indirect gap in Figure [1.](#page-3-0) The computational details can be found in Appendix [B.](#page-21-0)

In practice, we simulate supercell models including 100 atoms for the weak locality test and 200 atoms for the strong locality test, respectively.

FIGURE 4. 1D chain: Nearsightedness in homogeneous system with fixed $\text{gap}_{+} =$ 2.0 (left) and $\text{gap}_- = 0.01$ (right); cf. Theorem [3.1.](#page-4-2)

gap_{+}	2.0	$1.0\,$	0.5	0.25
	slope -0.2456 -0.1194 -0.0649 -0.0291			

Table 1. Slopes for the decay curves in Figure [4](#page-8-0) (b): the absolute values of slopes decay by half as gap_{+} decreases by half.

FIGURE 5. 1D chain: the nearsightedness with local perturbations; cf. Theorem [3.4](#page-5-2)

FIGURE 6. 1D chain: the nearsightedness with global perturbations; cf. Remark [3.7](#page-6-1)

In Figure [4,](#page-8-0) we compare the decay of the density matrix by fixing $\text{gap}_{+} = 2.0$ and varying $\textsf{gap}_- = 1/2, 1/8, 1/32, 1/128, 1/512$, where the decay curves coincide almost perfectly. Moreover, we also compare the results by fixing $\text{gap}_- = 0.01$ and taking $\text{gap}_+ = 2.0, 1.0, 0.5, 0.25$. which shows a linear dependence on gap_+ as displayed in Table [1,](#page-8-1) strongly supporting our analysis in Theorem [3.1.](#page-4-2)

In Figure [5](#page-9-0) and Figure [6,](#page-9-1) we conduct tests with admissible perturbations. Specifically, subfigures (a), (b), and (c) correspond to $\text{gap}_0 = 0.1, 0.01$ and 0.001, respectively. The perturbations have infinity norm of $\varepsilon = 10^{-6}, 10^{-4}, 10^{-2}, \text{ and } \ell_{\Upsilon}^2 \text{ norm of } \varepsilon = 10^{-5}, 10^{-3}, 10^{-1}, \text{ respectively.}$ The turning points of the curves in each figure shift forward gradually as $\mathsf{gap}_$ decreases and ε increases. Additionally, we observe that the influence of gap[−] becomes increasingly dominant as ε rises, which aligns perfectly with the analysis presented in Theorem [3.4.](#page-5-2)

In Figure [7,](#page-10-0) we plot the derivative of the density matrix \vert $\frac{\partial \rho_{\ell\ell}^{\text{ref}}}{\partial r_m}$ for $\ell = 1$ and $\textsf{gap}_{-} =$ $1.0, 0.1, 0.01, 0.001$, in both log-log and lin-log scales. We observe that the decay rate slows as gap[−] decreases. To further substantiate our conclusions, we provide an example from real systems with a small gap_ in the next section. Additionally, we present the slopes for Figure [7](#page-10-0) (b) in Table [2,](#page-10-1) which displays a square-root dependence on gap−, implying that our results may not be sharp in all situations.

Nevertheless, our results also show that there is a significant pre-asymptotic regime that is not described by our analysis, but which captures relevant scales. We are unaware of a technique to explain the decay in this regime.

gap_{-}	slope	c gap $\frac{\alpha}{\alpha}$
0.1	-0.4711	-0.4700
0.01	-0.1385	-0.1451
0.001	-0.0556 -0.0448	

Table 2. Slopes for the decay curves in Figure [7](#page-10-0) (b): the third column displays the optimal fitting between gap[−] and slope in a power-law form with parameters $c = -1.51$ and $\alpha = 0.51$.

FIGURE 7. 1D chain: the strong locality in homogeneous system is determined by \textsf{gap}_{-} rather than by \textsf{gap}_{+} ; cf. Proposition [3.9](#page-7-4)

4.2. Mg_2Si . The system we investigate here is an antifluorite-type compounds, a well-known semiconductor used in thermoelectric applications, characterized by a small indirect band gap. We conduct tests using the package DFTK.jl [\[17\]](#page-23-14), a library of Julia routines for working with plane-wave density-functional theory algorithms. Although the discussion in the paper focuses on the tight binding model, the property of locality is not limited to this model. Similar results can be found in [\[1,](#page-23-5) [18,](#page-23-8) [30\]](#page-24-1).

The energy bands for Mg_2Si are presented in Figure [2.](#page-4-0) The extrema of valence and conduction bands occur at the point Γ and X respectively, which results in a small indirect band gap around 0.21 eV. However, the gap_+ is relatively large around 1.8 eV.

We use a supercell model consisting of $4 \times 4 \times 4$ unit cells to verify the nearsightedness and strong locality. To make the results more convincing, we also present the corresponding tests for C. Figures (a) to (d) display the decay in homogeneous systems and the perturbed ones with infinity norm of $\varepsilon = 0.01$. The results confirm to a surprising degree that our analysis is applicable to systems of this significantly increased complexity.

FIGURE 8. Mg₂Si and C: the nearsightedness property of homogeneous and perturbed systems; cf. Theorem [3.1](#page-4-2) and Theorem [3.4.](#page-5-2)

Finally, we examine the strong locality of Mg2Si and C by evaluating the energy Hessian in homogeneous systems, which we computed using the finite difference of site forces $[F(\rho^{\text{ref}})]_i, i \in$ $Λ$, defined by

$$
d^2 E_{ij} := \left| \frac{\partial^2 E(\rho^{\text{ref}})}{\partial \mathbf{r}_i \partial \mathbf{r}_j} \right| \approx \left| \frac{[F(\rho(u_\varepsilon))]_i - [F(\rho^{\text{ref}})]_i}{\partial \mathbf{r}_j} \right|,
$$
(4.3)

where $u_{\varepsilon}(\ell) = 0$ if $\ell \neq j$ and $u(j) = \varepsilon j$ for some $\varepsilon > 0$ as the step length. In Figure [9,](#page-11-0) by plotting the data (r_{ij}, d^2E_{ij}) , we find it challenging to capture the decay in Mg₂Si due to its small gap₋. In contrast, the decay is clearly visible in C, which has a moderate gap_{-} , comparable to gap_{+} .

FIGURE 9. Mg₂Si and C: the strong locality in a homogeneous system depends on \textsf{gap}_- rather than \textsf{gap}_+ ; cf. Proposition [3.9.](#page-7-4)

5. Conclusions

In this paper, we refined our understanding of the dependence of nearsightedness in linear tight binding models on the band structure. We focussed on materials with indirect band gaps, which are usually small in semiconductors such as Si and Mg_2Si . In these systems, existing results suggest that small gaps theoretically render the locality negligible.

By performing the locality analysis in reciprocal space, we obtained a sharper estimate that highlights how the off-diagonal decay of the density matrix depends on gap_{+} , which is larger than gap−, as shown in Figure [2.](#page-4-0) That is, in the small gap limit, the nearsightedness property can still be maintained as long as $\text{gap}_+ \gg \text{gap}_-$. In this context, our results explain why some small gapped systems still exhibit fast decay of local operators, as shown in Figure [4](#page-8-0) for the 1D toy model and Figure [8](#page-11-1) for 3D systems.

Moreover, we also demonstrated that the impact of perturbations decays as the lattice sites move far away from the perturbations, and this decay is controlled by gap[−] and the norm of perturbations. Regarding strong locality (e.g., interatomic interactions), our results, combined with those in [\[27\]](#page-24-2), indicate that strong locality depends on gap[−] and thus may lose fast decay in small gapped systems when considering the Hessian of energy or forces, as shown in Figure [9.](#page-11-0) However, the results in Figure [7](#page-10-0) and Table [2](#page-10-1) suggest that, under certain circumstances, the decay exhibits the square-root behaviour with respect to gap−, indicating that our results may not be sharp. A detailed analysis of this effect will be pursued in future work.

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6. Proofs of the Main Results

6.1. Proof of Theorem [3.1.](#page-4-2) In preparation of the proof, we begin by proving a result on perturbations of the spectrum of \mathcal{H}_{ξ} :

Lemma 6.1 (Perturbations of the Spectrum). *. Let H_{ξ} be the form of [\(2.8\)](#page-2-1). There exists a positive constant c_r independent of ξ , such that

$$
\sigma\left(\mathcal{H}_{\boldsymbol{\xi}+i\boldsymbol{\zeta}}\right)\subset B_{c_r|\boldsymbol{\zeta}|}\left(\sigma\big(\mathcal{H}_{\boldsymbol{\xi}}\big)\right),\quad\forall\boldsymbol{\zeta}\in\mathbb{R}^d\,\,\text{with}\,\,|\boldsymbol{\zeta}|\leq\frac{1}{2}\gamma_0,
$$

where $c_r = ch_0 \gamma_0^{-(d+1)}$ with c depending on d, \mathfrak{m}, M and $N_{\rm b}$.

Proof. According to Appendix [A,](#page-20-0) for all $1 \le a, b \le N_b$ and $\ell_0, k_0 \in \Lambda_0 = \Gamma \cap \Lambda$, we have

$$
\left[\mathcal{H}_{\xi+i\zeta}\right]_{\ell_0k_0}^{ab} = \sum_{\alpha \in \mathbb{Z}^d} \left([\mathcal{H}^{\text{ref}}]_{\ell_0+\mathsf{A}\alpha,k_0}^{ab} e^{(\ell_0-k_0+\mathsf{A}\alpha)\cdot\zeta} \right) e^{-i(\ell_0-k_0+\mathsf{A}\alpha)\cdot\zeta},
$$

and this yields that

$$
\left| \left[\mathcal{H}_{\xi + i\zeta} \right]_{\ell_0 k_0}^{ab} - \left[\mathcal{H}_{\xi} \right]_{\ell_0 k_0}^{ab} \right| = \left| \sum_{\alpha \in \mathbb{Z}^d} \left[\mathcal{H}^{\text{ref}} \right]_{\ell_0 + \mathsf{A}\alpha, k_0}^{ab} \left(e^{(\ell_0 - k_0 + \mathsf{A}\alpha) \cdot \zeta} - 1 \right) \right|
$$

$$
\leq h_0 \sum_{\alpha \in \mathbb{Z}^d} e^{-\gamma_0 |\ell_0 - k_0 + \mathsf{A}\alpha|} \left(e^{|\ell_0 - k_0 + \mathsf{A}\alpha| |\zeta|} - 1 \right).
$$

For fixed ℓ_0, k_0 , we define the above sum in brackets as the function

$$
F(\beta) = \sum_{\alpha \in \mathbb{Z}^d} e^{-\gamma_0 |\ell_0 - k_0 + A\alpha|} \left(e^{\beta |\ell_0 - k_0 + A\alpha|} - 1 \right),
$$

which is well-defined and differentiable as $0 \leq \beta \leq \frac{1}{2}$ $\frac{1}{2}\gamma_0$. Additionally, we see that $F(0) = 0$ and the derivative satisfies

$$
F'(\beta) = \sum_{\alpha \in \mathbb{Z}^d} e^{-(\gamma_0 - \beta)|\ell_0 - k_0 + A\alpha|} |\ell_0 - k_0 + A\alpha| \le \sum_{\alpha \in \mathbb{Z}^d} e^{-\frac{1}{2}\gamma_0|\ell_0 - k_0 + A\alpha|} |\ell_0 - k_0 + A\alpha| \le \frac{C_{\mathfrak{m},d}}{\gamma_0^{d+1}},
$$

where $C_{\mathfrak{m},d}$ is a constant depending on \mathfrak{m} and d. In particular, we have $|F(\beta)| \leq \frac{C_{\mathfrak{m},d}}{\gamma_0^{d+1}}\beta$. Based on these, we can control the difference of $\mathcal{H}_{\xi+i\zeta}$ and \mathcal{H}_{ξ} by $|\zeta|$ as follows

$$
\|\mathcal{H}_{\xi+i\zeta} - \mathcal{H}_{\xi}\|_{\mathrm{F}}^{2} = \sum_{\substack{\ell_{0},k_{0}\in\Lambda_{0} \\ 1 \le a,b \le N_{\mathrm{b}}}} \left| \left[\mathcal{H}_{\xi+i\zeta}\right]_{\ell_{0}k_{0}}^{ab} - \left[\mathcal{H}_{\xi}\right]_{\ell_{0}k_{0}}^{ab} \right|^{2} \n\le (N_{\mathrm{b}}h_{0})^{2} \sum_{\substack{\ell_{0},k_{0}\in\Lambda_{0} \\ \ell_{0},k_{0}\in\Lambda_{0}}} \left(\sum_{\alpha\in\mathbb{Z}^{d}} e^{-\gamma_{0}|\ell_{0}-k_{0}+A\alpha|} \left(e^{|\ell_{0}-k_{0}+A\alpha||\zeta|}-1\right)\right)^{2} \n\le (MN_{\mathrm{b}}h_{0})^{2} \sup_{\ell_{0},k_{0}\in\Lambda_{0}} \left(\sum_{\alpha\in\mathbb{Z}^{d}} e^{-\gamma_{0}|\ell_{0}-k_{0}+A\alpha|} \left(e^{|\ell_{0}-k_{0}+A\alpha||\zeta|}-1\right)\right)^{2} \n\le \left(C_{\mathrm{m},d}MN_{\mathrm{b}}h_{0}\gamma_{0}^{-(d+1)}\right)^{2} |\zeta|^{2}
$$
\n(6.1)

for all $|\zeta| \leq \frac{1}{2}\gamma_0$. By Weyl's theorem [\[19\]](#page-23-20), we have

$$
\text{dist}\left(\sigma\big(\mathcal{H}_{\xi}\big),\,\sigma\big(\mathcal{H}_{\xi+i\zeta}\big)\right) \leq \|\mathcal{H}_{\xi+i\zeta} - \mathcal{H}_{\xi}\|_{\mathrm{F}} \leq c_{\mathrm{r}}|\zeta|,\tag{6.2}
$$

where $c_r := ch_0 \gamma_0^{-(d+1)}$ with $c > 0$ depending on d, \mathfrak{m}, m and N_b . Therefore, we can conclude that

$$
\sigma\left(\mathcal{H}_{\xi+i\zeta}\right) \subset B_{c_r|\zeta|}\left(\sigma\big(\mathcal{H}_{\xi}\big)\right),\tag{1}
$$
 as required.
$$
\Box
$$

Now we will use Lemma [6.1](#page-12-1) to prove Theorem [3.1:](#page-4-2)

Proof of Theorem [3.1.](#page-4-2) Let us choose a simple, closed and positively oriented contour $\mathscr C$ containing the line segment $i[-R, R]$ for some $R > 0$ (chosen later to be sufficiently large) and such that $\varepsilon_F + \mathscr{C}$ encircles the valence bands $\{\varepsilon_n\}_{n\leq N_0}$ of \mathcal{H}^{ref} and satisfies

$$
\text{dist}\left(\varepsilon_{\text{F}} + \mathscr{C}, \sigma(\mathcal{H}^{\text{ref}})\right) > 0. \tag{6.3}
$$

Applying the contour integral representation in [\(3.5\)](#page-5-3), we have

$$
\rho_{\ell k,ab}^{\text{ref}} = \int_{\Gamma^*} \left[\oint_{\mathscr{C} + \nu(\xi)} (z - \mathcal{H}_{\xi})^{-1} \frac{dz}{2\pi i} \right]_{\ell_0 k_0, ab} e^{i\xi \cdot (\ell - k)} d\xi, \tag{6.4}
$$

where $\nu : \Gamma^* \to \mathbb{C}$ is a mapping to be determined, satisfying $\varepsilon_{N_0}(\xi) < \nu(\xi) < \varepsilon_{N_0+1}(\xi)$ for all $\xi \in \Gamma^*$. For simplicity, let us define $R_z(\xi) := (z - \mathcal{H}_\xi)^{-1}$ and note

$$
\widehat{\rho}(\boldsymbol{\xi}) \coloneqq \oint_{\mathscr{C}+\nu(\boldsymbol{\xi})} (z - \mathcal{H}_{\boldsymbol{\xi}})^{-1} \frac{\mathrm{d}z}{2\pi i} = \oint_{\mathscr{C}+\nu(\boldsymbol{\xi})} R_z(\boldsymbol{\xi}) \frac{\mathrm{d}z}{2\pi i} \quad \in \mathbb{C}^{MN_{\mathrm{b}} \times MN_{\mathrm{b}}},\tag{6.5}
$$

then [\(6.4\)](#page-13-0) can be rewritten as

$$
\rho_{\ell k,ab}^{\text{ref}} = \int_{\Gamma^*} \left[\widehat{\rho}(\boldsymbol{\xi}) \right]_{\ell_0 k_0, ab} e^{i \boldsymbol{\xi} \cdot (\ell - k)} \mathrm{d} \boldsymbol{\xi},\tag{6.6}
$$

thus the decay rate of $[\rho_{\ell k, ab}^{\text{ref}}]$ is related to the analyticity of $\xi \mapsto [\hat{\rho}(\xi)]_{\ell_0 k_0, ab}$ [\[31\]](#page-24-7), which is determined by the regularity of $\nu(\cdot)$ in $(\xi \xi)$ determined by the regularity of $\nu(\cdot)$ in [\(6.5\)](#page-13-1).

We first define $g(\xi) := \varepsilon_{N_0+1}(\xi) - \varepsilon_{N_0}(\xi)$ and note that $\text{gap}_+ = \min_{\Gamma^*} g$. Next, introduce $\alpha > 0$ to be determined later, and

$$
D_{\mathrm{R}} \coloneqq \left\{ \boldsymbol{\xi} + i\boldsymbol{\zeta} : \boldsymbol{\xi}, \boldsymbol{\zeta} \in \mathbb{R}^d, |\boldsymbol{\zeta}| \le \min\left\{ \frac{1}{2}\gamma_0, \frac{\alpha}{c_r} \mathsf{gap}_+ \right\} \right\} \tag{6.7}
$$

so that $\sigma(\mathcal{H}_{\xi+i\zeta}) \subset B_{\alpha\text{gap}_+}(\sigma(\mathcal{H}_{\xi}))$ for $\xi + i\zeta \in D_{\mathcal{R}}$ with $\xi, \zeta \in \mathbb{R}^d$. The mapping $\nu_0 \colon \mathbb{C}^d \to \mathbb{C}$ defined by

$$
\nu_0(\boldsymbol{\xi} + i\boldsymbol{\zeta}) \coloneqq \frac{\varepsilon_{N_0}(\boldsymbol{\xi}) + \varepsilon_{N_0+1}(\boldsymbol{\xi})}{2}, \qquad \boldsymbol{\xi}, \boldsymbol{\zeta} \in \mathbb{R}^d \tag{6.8}
$$

is continuous on D_R and hence admits a polynomial approximation $\nu: D_R \to \mathbb{C}$ with

$$
\left|\nu(\boldsymbol{\xi} + i\boldsymbol{\zeta}) - \nu_0(\boldsymbol{\xi} + i\boldsymbol{\zeta})\right| < \frac{\alpha}{2} \mathsf{gap}_+, \quad \boldsymbol{\xi} + i\boldsymbol{\zeta} \in D_\mathrm{R}.\tag{6.9}
$$

We therefore have $\nu(\boldsymbol{\xi} + i\boldsymbol{\zeta}) \in B_{\frac{\alpha}{2} \text{gap}_+}(\frac{1}{2})$ $\frac{1}{2}(\varepsilon_{N_0}(\boldsymbol{\xi}) + \varepsilon_{N_0+1}(\boldsymbol{\xi}))$ and thus

$$
\operatorname{dist}(\nu(\xi+i\zeta),\sigma(\mathcal{H}_{\xi+i\zeta}))\geq \frac{\mathsf{g}(\xi)-3\alpha\mathsf{gap}_+}{2}\geq \frac{1-3\alpha}{2}\mathsf{g}(\xi).
$$

We choose $\alpha \coloneqq \frac{1}{6}$ $\frac{1}{6}$ and R sufficiently large (recall, $i[-R, R] \subset \mathscr{C}$) so that dist $(z, \sigma(\mathcal{H}_{\xi + i\zeta})) \ge$ 1 $\frac{1}{4}\mathsf{g}(\boldsymbol{\xi})$ for all $z \in \nu(\boldsymbol{\xi}) + \mathscr{C}$ and $\boldsymbol{\xi} + i\boldsymbol{\zeta} \in D_{\mathbb{R}}$. Since $\nu \colon \mathbb{C}^d \to \mathbb{C}$ is analytic on $D_{\mathbb{R}}$, we have that $\hat{\rho}$ extends to an analytic function on D_{R} .

Therefore, for all $|\zeta| \leq \eta_+ \coloneq \min\{\frac{1}{2}$ $rac{1}{2}\gamma_0, \frac{\alpha}{c_1}$ $\frac{\alpha}{c_r}$ gap₊}, we have

$$
C^2 \coloneqq \int_{\Gamma^*} |\widehat{\rho}(\boldsymbol{\xi} + i\boldsymbol{\zeta})_{\ell_0 k_0, ab}|^2 \mathrm{d}\boldsymbol{\xi} = \sum_k |\rho_{\ell k, ab}^{\text{ref}}|^2 e^{2\boldsymbol{\zeta} \cdot (\ell - k)} < \infty. \tag{6.10}
$$

That is, we have the required bound $\left|\rho_{\ell k, ab}^{\text{ref}}\right| \leq Ce^{-\eta + r_{\ell k}}$.

Finally, we may show the dependence of C by noticing that,

$$
C^2 \leq \int_{\Gamma^*} \left(\frac{\ell(\mathscr{C})}{2\pi} \sup_{z \in \nu(\xi + i\zeta) + \mathscr{C}} |R_z(\xi + i\zeta)_{\ell_0 k_0, ab}| \right)^2 d\xi \leq \left(\frac{2\ell(\mathscr{C})}{\pi} \right)^2 \int_{\Gamma^*} g(\xi)^{-2} d\xi \qquad (6.11)
$$

where $\ell(\mathscr{C})$ denotes the length of the contour. Here, we have used the fact that $|R_z(\xi)_{\ell_0 k_0, ab}| \leq$ $\mathrm{dist}\big(z,\sigma(\mathcal{H}_{\boldsymbol{\xi}})\big)^{-1}\leq 4\mathsf{g}(\boldsymbol{\xi})^{-1}$. □

6.2. Proof of Theorem [3.4.](#page-5-2) In order to prove the conclusion, we require some preliminary results from [\[27\]](#page-24-2). Here we will restate these conclusions in our setting, and give some variants to establish a foundation for the subsequent proof.

We start with an improved Combes–Thomas resolvent estimate:

Lemma 6.2. Suppose $u \in \text{Adm}(\Lambda)$ and $z \in \mathbb{C}$ such that dist $(z, \sigma(\mathcal{H}^{\text{ref}})) \geq \mathfrak{d}^{\text{ref}}$ and dist $(z, \sigma(\mathcal{H}(u))) \geq \mathfrak{d}(u)$ for some $\mathfrak{d}^{\text{ref}}, \mathfrak{d}(u) > 0$. Then,

$$
\left| \left(z - \mathcal{H}(u) \right)^{-1}_{\ell k, ab} \right| \leq \frac{4}{\mathfrak{d}^{\text{ref}}} e^{-\gamma_{\text{CT}}\left(\frac{1}{2}\mathfrak{d}^{\text{ref}}\right)r_{\ell k}} + C(u) e^{-\frac{1}{2}\gamma_{\text{CT}}\left(\frac{1}{2}\mathfrak{d}^{\text{ref}}\right)\left(|\ell| + |k|\right)},\tag{6.12}
$$

with $\gamma_{\text{CT}}(\frac{1}{2})$ $\frac{1}{2}$ $\mathfrak{d}^{\textup{ref}}$) = $c_0 \min\{1, \frac{1}{2}\}$ $\frac{1}{2}$ $\mathfrak{d}^{\text{ref}}\},$ and

$$
C(u) = C R_1^d e^{\frac{1}{2}\gamma c \cdot \left(\frac{1}{2}\mathfrak{d}^{\text{ref}}\right)R_1} \frac{\|Du\|_{\ell_\Upsilon^2}}{\left(\mathfrak{d}^{\text{ref}}\right)^{d+4} \left(\mathfrak{d}(u)\right)^{d+1}},\tag{6.13}
$$

where $c_0, C > 0$ depend only on d, $\mathfrak{m}, h_0, \gamma_0, N_{\rm b}, M$, and $R_1 > 0$ is sufficiently large such that $||Du||_{\ell^2_{\Upsilon}(\Lambda \setminus B_{R_1})} \leq c_1 \mathfrak{d}^{\text{ref}}$ for some $c_1 > 0$. In particular, for sufficiently small $||Du||_{\ell^2_{\Upsilon}}$, R_1 can be chosen arbitrarily.

Proof. The point is mainly based on the approximation of $\mathcal{H}(u)$ by the finite rank update of \mathcal{H}^{ref} [\[27\]](#page-24-2). We summarise the proof here, as parts of the ideas will be revisited in the subsequent discussion. [\[27,](#page-24-2) Lemma 5.4] states that, for each $\delta > 0$, there exist $R_{\delta} > 0$ (depending on δ) and operators $P_{\delta}(u)$, $P_{\text{loc}}(u)$ such that

$$
\mathcal{H}(u) = \mathcal{H}^{\text{ref}} + P_{\delta}(u) + P_{\text{loc}}(u),\tag{6.14}
$$

where $||P_\delta(u)||_F \leq \delta$, and $[P_{\text{loc}}(u)]_{\ell k}^{ab} = [\mathcal{H}(u) - \mathcal{H}^{\text{ref}}]_{\ell k}^{ab}$ if $(\ell, k) \in B_{R_\delta} \times B_{R_\delta}$; else, $[P_{\text{loc}}(u)]_{\ell k}^{ab} = 0$. That is, we can decompose $\mathcal{H}(u) - \mathcal{H}^{\text{ref}}$ into two parts: P_{δ} and P_{loc} , which are small in terms of Frobenius norm and rank, respectively. As for the selection of R_{δ} , by [\[27,](#page-24-2) Lemma 5.4], we can first choose a sufficiently large $R_1 > 0$ satisfying $|u(\ell) - u(k)| \leq \mathfrak{m} |\ell - k|$ for all $\ell, k \in \Lambda \setminus B_{R_1}$, so that

$$
\left|\mathcal{H}(u)_{\ell k,ab} - \mathcal{H}_{\ell k,ab}^{\text{ref}}\right| \le h_0 e^{-\frac{\sqrt{3}}{2}\gamma_0 \mathfrak{m} r_{\ell k}} |u(\ell) - u(k)| \quad \forall \ell, k \in \Lambda \setminus B_{R_1},\tag{6.15}
$$

and then, for $\forall R_2 > 0$, the regularity of $\mathcal{H}(u)$ and \mathcal{H}^{ref} gives

$$
\sum_{\ell \in B_{R_1}} \sum_{\substack{k \in \Lambda \backslash B_{R_1} \\ |\ell - k| > R_2}} \left| \mathcal{H}(u)_{\ell k, ab} - \mathcal{H}_{\ell k, ab}^{\text{ref}} \right|^2 \le C \sum_{\ell \in B_{R_1}} \sum_{\substack{k \in \Lambda \backslash B_{R_1} \\ |\ell - k| > R_2}} e^{-2\gamma_0 \mathfrak{m} |\ell - k|} \le C R_1^d e^{-\gamma_0 \mathfrak{m} R_2},\tag{6.16}
$$

where $C > 0$ depends on d, $\mathfrak{m}, \gamma_0, h_0$. Through [\(6.15\)](#page-15-0) and [\(6.16\)](#page-15-1), we have

$$
||P_{\delta}||_{\mathrm{F}}^{2} = \sum_{1 \le a,b \le N_{\mathrm{b}}} \Big(\sum_{\ell,k \in \Lambda \backslash B_{R_{1}}} + \sum_{\ell \in B_{R_{1}}} \sum_{\substack{k \in \Lambda \backslash B_{R_{1}} \\ |\ell - k| > R_{2}}} \Big) \Big| \mathcal{H}(u)_{\ell k,ab} - \mathcal{H}_{\ell k,ab}^{\mathrm{ref}} \Big|^{2}
$$

$$
\le C \big(||Du||_{\ell_{\Upsilon}^{2}(\Lambda \backslash B_{R_{1}})}^{2} + R_{1}^{d} e^{-\gamma_{0} \mathfrak{m} R_{2}} \big), \tag{6.17}
$$

which implies the value can be arbitrarily small by choosing R_1 and then R_2 sufficiently large. Specifically, we can choose R_1, R_2 with

$$
C\big(\|Du\|_{\ell^2_{\Upsilon}(\Lambda \setminus B_{R_1})}^2 + R_1^d e^{-\gamma_0 \mathfrak{m} R_2}\big) \le \big(\frac{1}{2} \mathfrak{d}^{\text{ref}}\big)^2,\tag{6.18}
$$

By setting $R_{\delta} = R_1 + R_2$, we obtain $||P_{\delta}||_F \leq \frac{1}{2}$ $\frac{1}{2}$ $\mathfrak{d}^{\text{ref}}$ and P_{loc} satisfying the identity [\(6.14\)](#page-15-2), where the choice of R_{δ} depends on $\mathfrak{d}^{\text{ref}}$.

Since $P_{loc}(u)$ has finite rank, we can perform a decomposition for the submatrix $P_{loc}|_{B_{R_\delta}\times B_{R_\delta}}:=$ $\{(P_{\text{loc}})_{ij}\}_{(i,j)\in B_{R_{\delta}}\times B_{R_{\delta}}}$, by operators U, V satisfying $P_{\text{loc}} = UV$, where $U|_{B_{R_{\delta}}\times B_{R_{\delta}}}$ is orthogonal and $U_{\ell i} = 0, V_{j\ell} = 0$, for $\forall i, j \in B_{R_\delta}$ and $\ell \in \Lambda \backslash B_{R_\delta}$. For brevity, we denote $A := z - \mathcal{H}^{\text{ref}} - P_\delta(u)$, then $A - P_{\text{loc}}(u) = z - \mathcal{H}(u)$. Applying the Woodbury identity [\[16\]](#page-23-21) for $A - P_{\text{loc}}(u)$ yields

$$
(A - P_{loc}(u))^{-1} = (A - UV)^{-1} = A^{-1} + A^{-1}U(I - VA^{-1}U)^{-1}VA^{-1},
$$
(6.19)

where I is the unit matrix of size $|B_{R_\delta}|\times |B_{R_\delta}|$. Notice that $U(I-VA^{-1}U)^{-1}V$ also has finite rank. Thus, for $\forall \ell, k \in B_{R_{\delta}}, 1 \le a, b \le N_{\delta}$, by following [\[27\]](#page-24-2), we have

$$
\left| \left[U(I - VA^{-1}U)^{-1} V \right]_{\ell k, ab} \right| = \left| \left[A(A - P_{\text{loc}}(u))^{-1} P_{\text{loc}}(u) \right]_{\ell k, ab} \right|
$$
\n
$$
\leq \sum_{m,n:|\mathbf{r}_n| \leq R_{\delta}} \sum_{a_1 b_1} \left| (z - \mathcal{H}^{\text{ref}} - P_{\delta}(u))_{\ell m, a a_1} \right| \left| (z - \mathcal{H}(u))_{mn, a_1 b_1}^{-1} \right| \left| P_{\text{loc}}(u)_{nk, b_1 b} \right|
$$
\n
$$
\leq \frac{2N_{\text{b}}(|z| + h_0)}{\mathfrak{d}(u)} \left(\sum_{m,n:|\mathbf{r}_n| \leq R_{\delta}} e^{-\gamma_0 r_{\ell m}} e^{-\gamma_0 \text{T}(\mathfrak{d}(u)) r_{mn}} \right) \max_{\ell,k \in B_{R_{\delta}}} \left| P_{\text{loc}}(u)_{\ell k, ab} \right|
$$
\n
$$
\leq \frac{c}{(\mathfrak{d}(u))^{d+1}} \max_{\ell,k \in B_{R_{\delta}}} \left| P_{\text{loc}}(u)_{\ell k, ab} \right|
$$
\n
$$
\left| \sum_{1 \leq a, b \leq N_{\text{b}}} \left| P_{\text{loc}}(u)_{\ell k, ab} \right|
$$
\n(6.20)

where $c > 0$ depends on $h_0, \gamma_0, \mathfrak{m}, d, N_b, M$, and is bounded independently of z since we are considering z in a bounded set. From the above proof of (6.14) , we can control the maximum of $P_{\text{loc}}(u)$ in $B_{R_{\delta}}$ by

$$
\max_{\ell,k \in B_{R_{\delta}} \atop 1 \le a,b \le N_{\rm b}} |P_{\rm loc}(u)| = \max_{\ell,k \in B_{R_{\delta}} \atop 1 \le a,b \le N_{\rm b}} \left| \left[\mathcal{H}(u) - \mathcal{H}^{\rm ref} - P_{\delta} \right]_{\ell k}^{ab} \right| = \max_{\ell,k \in B_{R_{\delta}} \atop 1 \le a,b \le N_{\rm b}} \left| \left[\mathcal{H}(u) - \mathcal{H}^{\rm ref} \right]_{\ell k}^{ab} \right|
$$

\n
$$
\le \max_{\ell,k \in B_{R_{\delta}} \atop 1 \le a,b \le N_{\rm b}} \left| \nabla h_{\ell k}^{ab}(\nu_{\theta}) \cdot \left[u(\ell) - u(k) \right] \right| \le C \|Du\|_{\ell^2_{\Upsilon}(B_{R_{\delta}})}, \tag{6.21}
$$

where we applied mean value theorem and $\mathbf{v}_{\theta} := (1 - \theta) \mathbf{r}_{\ell k}(u) + \theta \mathbf{r}_{\ell k}$ for some $\theta \in [0, 1],$ and the constant $C > 0$ depends only on $d, \mathfrak{m}, h_0, \gamma_0$. Additionally, as $||P_\delta||_F < \frac{1}{2}$ $\frac{1}{2}$ $\mathfrak{d}^{\text{ref}}$, the Combes–Thomas estimate [\(3.4\)](#page-4-4) for A is

$$
\left|A_{\ell k,ab}^{-1}\right|\leq \frac{4}{\mathfrak{d}^{\textup{ref}}}e^{-\gamma_{\textup{CT}}(\frac{1}{2}\mathfrak{d}^{\textup{ref}})r_{\ell k}}.
$$

Combining this with [\(6.20\)](#page-15-3), [\(6.21\)](#page-16-0) and the exponential sum estimate in Lemma [C.1,](#page-22-0) the second term of [\(6.19\)](#page-15-4) is bounded by

$$
\left| \left[A^{-1}U \left(I - VA^{-1}U \right)^{-1} VA^{-1} \right]_{\ell k, ab} \right| \leq \frac{c \|Du\|_{\ell^2_{\Upsilon}(B_{R_{\delta}})}}{(\mathfrak{d}^{\text{ref}})^2 (\mathfrak{d}(u))^{d+1}} \sum_{\ell_1, \ell_2 \colon |\ell_i| \leq R_{\delta}} e^{-\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}})(r_{\ell \ell_1} + r_{\ell_2 k})}
$$

$$
\leq \frac{c \|Du\|_{\ell^2_{\Upsilon}}}{(\mathfrak{d}^{\text{ref}})^2 (\mathfrak{d}(u))^{d+1}} \left(\frac{C_d e^{\frac{1}{2}\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}})R_{\delta}}}{(\mathfrak{m}\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}}))^d} e^{-\frac{1}{2}\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}})(|\ell|+|\kappa|)} \right)
$$

$$
\leq C(u) e^{-\frac{1}{2}\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}})(|\ell|+|\kappa|)}, \tag{6.22}
$$

where $C(u) := Ce^{\frac{1}{2}\gamma c \mathrm{\text{T}}(\frac{1}{2}\mathfrak{d}^{\mathrm{ref}})R_{\delta}} \|Du\|_{\ell^2_{\gamma}} / \big((\mathfrak{d}^{\mathrm{ref}})^{d+2}(\mathfrak{d}(u)\big)^{d+1}\big)$ with C depending on $h_0, \gamma_0, \mathfrak{m}, d, N_{\mathrm{b}}, M$. Noticing that, from [\(6.18\)](#page-15-5), we can find some constants $C_1, C_2 > 0$ such that $e^{\frac{1}{2}\gamma c_T(\frac{1}{2}e^{rcf})R_2}$ $C_1 R_1^d (\mathfrak{d}^{\text{ref}})^{-2}$, and $||Du||_{\ell^2_{\Upsilon}(\Lambda \backslash B_{R_1})} < C_2 \mathfrak{d}^{\text{ref}}$. Hence, the prefactor $C(u)$ can be written as

$$
C(u) = CR_1^d e^{\frac{1}{2}\gamma c \operatorname{tr}(\frac{1}{2}\mathfrak{d}^{\text{ref}})R_1} \frac{\|Du\|_{\ell^2_{\Upsilon}}}{(\mathfrak{d}^{\text{ref}})^{d+4}(\mathfrak{d}(u))^{d+1}}.
$$

Finally, taking [\(3.4\)](#page-4-4) and [\(6.22\)](#page-16-1) into the entry of [\(6.19\)](#page-15-4), we conclude that

$$
\left| (z - \mathcal{H}(u))_{\ell k, ab}^{-1} \right| \le \left| A_{\ell k, ab}^{-1} \right| + \left| \left[A^{-1} U \left(I - V A^{-1} U \right)^{-1} V A^{-1} \right]_{\ell k, ab} \right|
$$
\n
$$
\le \frac{4}{\mathfrak{d}^{\text{ref}}} e^{-\gamma_{\text{CT}}\left(\frac{1}{2}\mathfrak{d}^{\text{ref}}\right) r_{\ell k}} + C(u) e^{-\frac{1}{2}\gamma_{\text{CT}}\left(\frac{1}{2}\mathfrak{d}^{\text{ref}}\right) \left(|\ell| + |k| \right)}.
$$
\n(6.23)

$$
\Box
$$

Remark 6.3. By directly applying Lemma [6.2,](#page-14-1) we have

$$
\left| \left(z - \mathcal{H}(u) \right)^{-1}_{\ell k, ab} \right| \leq \left(\frac{4}{\mathfrak{d}^{\text{ref}}} e^{-\frac{1}{2}\gamma_{\text{CT}}\left(\frac{1}{2}\mathfrak{d}^{\text{ref}}\right)r_{\ell k}} + C(u) \right) e^{-\frac{1}{2}\gamma_{\text{CT}}\left(\frac{1}{2}\mathfrak{d}^{\text{ref}}\right)r_{\ell k}} := \tilde{C}(u) e^{-\frac{1}{2}\gamma_{\text{CT}}\left(\frac{1}{2}\mathfrak{d}^{\text{ref}}\right)r_{\ell k}}. (6.24)
$$

Additionally, we can always choose $\mathscr C$ in the above estimation satisfying

$$
\mathrm{dist}(\mathscr{C}, \sigma(\mathcal{H}^{\mathrm{ref}})) \geq \frac{1}{2}\mathsf{gap}_-,
$$

so that the above estimate can be written in terms of gap_{-} and $\gamma_{\text{CT}}(\frac{1}{2})$ $\frac{1}{2}$ gap_−).

With the above preparation, we now proceed to the proof of Theorem [3.4:](#page-5-2)

Proof of Theorem [3.4.](#page-5-2) Notice that the following inequality always holds

$$
\left|\rho(u)_{\ell k,ab}\right| \le \left|\rho_{\ell k,ab}^{\text{ref}}\right| + \left|\rho(u)_{\ell k,ab} - \rho_{\ell k,ab}^{\text{ref}}\right| \quad \forall \ell, k \in \Lambda, 1 \le a, b \le N_b. \tag{6.25}
$$

To obtain the result, it suffices to only estimate the last term in [\(6.25\)](#page-17-0), for the control of the first term has been given by Theorem [3.1.](#page-4-2) The difference between $\rho(u)$ and ρ^{ref} is bounded by

$$
|\rho(u)_{\ell k,ab} - \rho_{\ell k,ab}^{\text{ref}}| = \left| \oint_{\mathscr{C}} \left[(z - \mathcal{H}(u))^{-1} - (z - \mathcal{H}^{\text{ref}})^{-1} \right]_{\ell k,ab} \frac{dz}{2\pi i} \right|
$$

\n
$$
= \left| \oint_{\mathscr{C}} \left[(z - \mathcal{H}(u))^{-1} (\mathcal{H}(u) - \mathcal{H}^{\text{ref}}) (z - \mathcal{H}^{\text{ref}})^{-1} \right]_{\ell k,ab} \frac{dz}{2\pi i} \right|
$$

\n
$$
\leq C \Big(\sum_{m,n \in B_R} F(\ell, m, n, k) + \sum_{m \notin B_R \text{ or } n \notin B_R} F(\ell, m, n, k) \Big)
$$

\n
$$
=: C \big(T_1 + T_2 \big), \tag{6.26}
$$

where we define

$$
F(\ell,m,n,k) := \sum_{1 \leq b_1,c_1 \leq N_b} \left| \left(z - \mathcal{H}(u) \right)_{\ell m,ab_1}^{-1} \right| \cdot \left| \left[\mathcal{H}(u) - \mathcal{H}^{\text{ref}} \right]_{mn,b_1c_1} \right| \cdot \left| \left(z - \mathcal{H}^{\text{ref}} \right)_{nk,c_1b}^{-1} \right|.
$$

Here, we choose a sufficiently large R in (6.26) so that (6.15) still holds. Combining the regularity of Hamiltonians with Combes–Thomas estimate [\(3.4\)](#page-4-4) and its improved version [\(6.24\)](#page-16-2), we have

$$
T_1 = \sum_{m \in B_R \text{ or } n \in B_R} F(\ell, m, n, k)
$$

\n
$$
\leq \tilde{C}(u) \sum_{m \in B_R \text{ or } n \in B_R} e^{-\frac{1}{2}\gamma c \tau (\frac{1}{2}\mathfrak{d}^{\text{ref}}) r_{\ell m}} e^{-\gamma_0 \mathfrak{m} r_{mn}} e^{-\gamma c \tau (\mathfrak{d}^{\text{ref}}) r_{mk}}
$$

\n
$$
\leq \tilde{C}(u) \sum_{m \in B_R} e^{-\frac{1}{2}\gamma c \tau (\frac{1}{2}\mathfrak{d}^{\text{ref}}) r_{\ell m}} e^{-\frac{1}{2}\min{\gamma c \tau (\mathfrak{d}^{\text{ref}}), \gamma_0 \mathfrak{m}} r_{nk}} \leq \tilde{C}(u) \sum_{m \in B_R} e^{-4\eta_{-}(r_{\ell m} + r_{mk})}
$$

\n
$$
\leq \tilde{C}(u) \Big(e^{-2\eta_{-} \min_{m \in B_R} (r_{\ell m} + r_{mk})} \sum_{m \in \Lambda} e^{-2\eta_{-}(r_{\ell m} + r_{mk})} \Big)
$$

\n
$$
\leq \tilde{C}(u) e^{-2\eta_{-} \min_{m \in B_R} (r_{\ell m} + r_{mk})} e^{-\eta_{-} r_{\ell k}}
$$
\n(6.27)

where we denote

$$
\eta_{-} := \frac{1}{8} \min \{ \gamma_{\rm CT}(\frac{1}{2} \mathfrak{d}^{\rm ref}), \gamma_0 \mathfrak{m} \} = c_0 \min \{ h_0, \gamma_0^d \mathfrak{d}^{\rm ref} \},\tag{6.28}
$$

with some $c_0 > 0$ depends only on $\mathfrak{m}, d, h_0, \gamma_0$. Then, using [\(6.15\)](#page-15-0) and Hölder's inequality yields

$$
T_2 = \sum_{m,n \in \Lambda \backslash B_R} F(\ell,m,n,k)
$$

\n
$$
\leq \tilde{C}(u) \sum_{m,n \in \Lambda \backslash B_R} e^{-\frac{1}{2}\gamma c \tau (\frac{1}{2}\mathfrak{d}^{\text{ref}}) r_{\ell m}} \Big(e^{-\frac{\sqrt{3}}{2}\gamma_0 \mathfrak{m} r_{mn}} |u(m) - u(n)|\Big)e^{-\gamma c \tau (\mathfrak{d}^{\text{ref}}) r_{nk}}\Big|
$$

\n
$$
\leq \tilde{C}(u) \Big(\sum_{m,n \in \Lambda \backslash B_R} e^{-\gamma c \tau (\frac{1}{2}\mathfrak{d}^{\text{ref}}) r_{\ell m}} e^{-(\sqrt{3}\gamma_0 \mathfrak{m} - 2\Upsilon) r_{mn}} e^{-2\gamma c \tau (\mathfrak{d}^{\text{ref}}) r_{nk}}\Big)^{\frac{1}{2}} \Big(\sum_{m,n \in \Lambda \backslash B_R} e^{-2\Upsilon r_{mn}} |u(m) - u(n)|^2\Big)^2
$$

\n
$$
\leq \tilde{C}(u) \|Du\|_{\ell^2_{\Upsilon}(\Lambda \backslash B_R)} \Big(\sum_{m,n \in \Lambda \backslash B_R} e^{-\gamma c \tau (\frac{1}{2}\mathfrak{d}^{\text{ref}}) r_{\ell m}} e^{-\frac{\sqrt{3}}{2}\gamma_0 \mathfrak{m} r_{mn}} e^{-2\gamma c \tau (\mathfrak{d}^{\text{ref}}) r_{nk}}\Big)^{\frac{1}{2}}
$$

\n
$$
\leq \tilde{C}(u) \|Du\|_{\ell^2_{\Upsilon}(\Lambda \backslash B_R)} \sum_{m,n \in \Lambda \backslash B_R} e^{-4\eta - (r_{\ell m} + r_{mn} + r_{nk})} \leq \tilde{C}(u) \|Du\|_{\ell^2_{\Upsilon}(\Lambda \backslash B_R)} \sum_{m \in \Lambda} e^{-2\eta - (r_{\ell m} + r_{mk})}
$$

\n
$$
\leq \tilde{C}(u) \|Du\|_{\ell^2_{\Upsilon}(\Lambda \backslash B_R)} e^{-\eta - r_{\ell k}}.
$$

\n(6.29)

From Lemma [C.1,](#page-22-0) we note that the prefactors in [\(6.27\)](#page-17-2) and [\(6.29\)](#page-17-3) are both independent of η as gap_ is small. Moreover, by choosing $\mathscr C$ satisfying dist $(\mathscr C,\sigma(\mathcal H^\mathrm{ref}))\geq \frac{1}{2}$ $\frac{1}{2}$ gap_, we can take gap_− in η _−. Finally, substituting [\(6.27\)](#page-17-2) and [\(6.29\)](#page-17-3) into [\(6.26\)](#page-17-1) draws the conclusion that

$$
\begin{split}\n|\rho(u)_{\ell k,ab} - \rho_{\ell k,ab}^{\text{ref}}| &\leq C(T_1 + T_2) \\
&\leq \frac{C||Du||_{\ell_{\Upsilon}^2}}{\mathfrak{d}^{\text{ref}}} \left(1 + \frac{R_1^d e^{\frac{1}{2}\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}})R_1}}{(\mathfrak{d}^{\text{ref}})^{d+3}(\mathfrak{d}(u))^{d+1}}\right) \left(||Du||_{\ell_{\Upsilon}^2(\Lambda \backslash B_R)} + e^{-2\eta - \min_{m \in B_R} [r_{\ell m} + r_{mk}]} \right) e^{-\eta - r_{\ell k}} \\
&\leq \frac{C||Du||_{\ell_{\Upsilon}^2}}{\mathsf{gap}_{-}} \left(1 + \frac{R_1^d e^{4\eta - R_1}}{\mathsf{gap}_{-}^{2d+4}}\right) \left(||Du||_{\ell_{\Upsilon}^2(\Lambda \backslash B_R)} + e^{-2\eta - \min_{m \in B_R} [r_{\ell m} + r_{mk}]} \right) e^{-\eta - r_{\ell k}} \\
&:= C_{\ell k}(u) e^{-\eta - r_{\ell k}}.\n\end{split} \tag{6.30}
$$

Taking this estimate into (6.25) completes the proof. \Box

6.3. Proof of the Proposition [3.9.](#page-7-4) We first provide an estimate for resolvents in homogeneous system exhibiting super-algebraic decay, which helps clarify the dependence of the strong locality on decay rate.

Lemma 6.4. Suppose H^{ref} satisfies (TB), and $z \in \mathscr{C}$ such that $\text{dist}(z, \sigma(\mathcal{H}^{\text{ref}})) \geq \mathfrak{d}^{\text{ref}}$ for some $\mathfrak{d}^{\text{ref}} > 0$. Then, for each $q \in \mathbb{Z}^+$, there exists a constant $C_q > 0$ such that

$$
\left| \left(z - \mathcal{H}^{\text{ref}} \right)^{-1}_{\ell k, ab} \right| \leq \frac{C_q(\mathfrak{d}^{\text{ref}})}{r_{\ell k}^q} e^{-\gamma_{\text{CT}}(\mathfrak{d}^{\text{ref}}) r_{\ell k}},\tag{6.31}
$$

for all $\ell \neq k, \ell, k \in \Lambda$, and $1 \leq a, b \leq N_b$, where the constant is defined by

$$
C_q(\mathfrak{d}^{\text{ref}}) := \begin{cases} cq!((\mathfrak{d}^{\text{ref}})^q - 1) / ((\mathfrak{d}^{\text{ref}})^{q+1}(\mathfrak{d}^{\text{ref}} - 1)), & \mathfrak{d}^{\text{ref}} \neq 1, \\ cq!(q/\mathfrak{d}^{\text{ref}}), & \mathfrak{d}^{\text{ref}} = 1, \end{cases}
$$
(6.32)

for some $c > 0$ depending only on h_0, γ_0, N_b, M .

Proof. Recall that in Appendix [A,](#page-20-0) we proved there exists a decomposition for \mathcal{H}^{ref} , denoted by $\mathcal{H}_{\xi} \in \mathbb{R}^{MN_{\mathrm{b}} \times MN_{\mathrm{b}}}, \xi \in \Gamma^*$. So the resolvent can be written as

$$
(z - \mathcal{H}^{\text{ref}})^{-1}_{\ell k, ab} = \int_{\Gamma^{\star}} (z - \mathcal{H}_{\xi})^{-1}_{\ell k, ab} e^{i\xi \cdot r_{\ell k}} d\xi.
$$
 (6.33)

By partial integration, we have

$$
(z - \mathcal{H}^{\text{ref}})^{-1}_{\ell k, ab} = \frac{i^{|\alpha|}}{[r_{\ell k}]^{\alpha}} \oint_{\Gamma^{\star}} \frac{\partial^{|\alpha|}}{\partial \xi^{\alpha}} \left((z - \mathcal{H}_{\xi})^{-1}_{\ell k, ab} \right) e^{i\xi \cdot r_{\ell k}} d\xi, \tag{6.34}
$$

where $\boldsymbol{\alpha} = (\alpha_1, \dots, \alpha_d) \in \mathbb{N}^d$ is the multi-index with $|\boldsymbol{\alpha}| := \sum_i \alpha_i$, and $[\boldsymbol{r}_{\ell k}]^{\boldsymbol{\alpha}} := \prod_i [\boldsymbol{r}_{\ell k}]_i^{\alpha_i}$. The first derivative of $(z - \mathcal{H}_{\xi})^{-1}$ is

$$
\frac{\partial}{\partial \xi_l} \left((z - \mathcal{H}_{\xi})^{-1} \right) = (z - \mathcal{H}_{\xi})^{-1} \frac{\partial \mathcal{H}_{\xi}}{\partial \xi_l} (z - \mathcal{H}_{\xi})^{-1}, \quad \forall 1 \le l \le d. \tag{6.35}
$$

For $|\alpha| = q \in \mathbb{N}, q > 1$, the higher order derivatives can be given by

$$
\frac{\partial^{|\alpha|}}{\partial \xi^{\alpha}} \left((z - \mathcal{H}_{\xi})^{-1} \right) = \sum_{n=1}^{q} \sum_{\substack{\beta_1, \dots, \beta_n \in \mathbb{N}^d \setminus \{0\} : \\ \alpha = \beta_1 + \dots + \beta_n}} \widehat{D}_{z, \xi}^{(n)} \left(\frac{\partial^{|\beta_1|} \mathcal{H}_{\xi}}{\partial \xi^{\beta_1}}, \dots, \frac{\partial^{|\beta_n|} \mathcal{H}_{\xi}}{\partial \xi^{\beta_n}} \right), \tag{6.36}
$$

where $\widehat{D}_{z,\xi}^{(n)}: (\mathbb{R}^{MN_{\rm b}\times MN_{\rm b}})^n \to \mathbb{R}^{MN_{\rm b}\times MN_{\rm b}}$ is given by

$$
\widehat{D}_{z,\xi}^{(n)}(X_1,\ldots,X_n) = (z - \mathcal{H}_{\xi})^{-1} \prod_{j=1}^n \left[X_j (z - \mathcal{H}_{\xi})^{-1} \right]. \tag{6.37}
$$

For all $\xi \in \Gamma^*, \widehat{D}_{z,\xi}^{(n)}$ is an analytic function as dist $(z, \sigma(\mathcal{H}^{\text{ref}})) \geq \mathfrak{d}^{\text{ref}}$. Thus, for all $|\zeta| \leq$ $\gamma_{\text{CT}}(\mathfrak{d}^{\text{ref}}), \boldsymbol{\zeta} \in \mathbb{R}^d$, we have

$$
\int_{\Gamma^*} \left| \widehat{D}^{(n)}_{z,\xi+i\zeta}(X_1,\ldots,X_n)_{\ell_0 k_0, ab} \right|^2 d\xi = \sum_{k \in \Lambda} \left[D^{(n)}_z(X_1,\ldots,X_n) \right]_{\ell k, ab}^2 e^{2\zeta \cdot r_{\ell k}} < \infty, \tag{6.38}
$$

where we define $[D_z^{(n)}]_{\ell k,ab} := \int_{\Gamma^*} \left[\widehat{D}_{z,\xi}^{(n)} \right]_{\ell_0 k_0,ab} e^{i\xi \cdot r_{\ell k}} d\xi$. Moreover, by solving the eigenvalue problem [\(A.1\)](#page-21-1), we have the eigenpairs $(\varepsilon_n(\xi), u_n(\xi))$ of \mathcal{H}_{ξ} , where $\{u_n(\xi)\}_n$ are orthonormal and continues in ξ , and then

$$
\left| (z - \mathcal{H}_{\xi})_{\ell_0 k_0, ab}^{-1} \right| = \left| \sum_{n=1}^{MN_b} \frac{[u_n(\xi) \otimes u_n(\xi)]_{\ell_0 k_0, ab}}{z - \varepsilon_n(\xi)} \right| \le CMN_b(\mathfrak{d}^{\text{ref}})^{-1}, \quad \forall \xi \in \Gamma^*, \tag{6.39}
$$

for some $C > 0$. From this and [\(6.37\)](#page-18-1), we obtain

$$
\left| \widehat{D}_{z,\xi+i\zeta}^{(n)}(X_1,\ldots,X_n)_{\ell_0k_0,ab} \right| \le C(\mathfrak{d}^{\text{ref}})^{-(n+1)} \prod_{j=1}^n \|X_j\|_{\infty} \tag{6.40}
$$

with $X_j = \partial^{|\beta_j|} \mathcal{H}_{\xi}/\partial \xi^{\beta_j}, j = 1, \ldots, n$, for some constant $C > 0$ depending on M, N_b . Combining (6.38) with (6.40) , in a similar manner as (6.10) , we obtain

$$
\left| \int_{\Gamma^*} \widehat{D}_{z,\xi}^{(n)} \left(X_1, \cdots, X_n \right)_{\ell_0 k_0, ab} e^{i\xi \cdot r_{\ell k}} d\xi \right| \le C \left(\mathfrak{d}^{\text{ref}} \right)^{-(n+1)} e^{-\gamma_{\text{CT}} (\mathfrak{d}^{\text{ref}}) r_{\ell k}}, \tag{6.41}
$$

with a constant C depending on X_j , $j = 1, \dots, n$. Note that, for each $1 \leq n \leq q$, there exits at most $d!n! \binom{n}{a}$ $\binom{n}{q} \lesssim q!$ terms of $\widehat{D}_{z,\xi}^{(n)}$ for the second sum in [\(6.36\)](#page-18-2). Using [\(6.34\)](#page-18-3), (6.36) and [\(6.41\)](#page-19-2), we arrive at

$$
\left| (z - \mathcal{H}^{\text{ref}})_{\ell k, ab}^{-1} \right| \leq \frac{C}{r_{\ell k}^{q}} \sum_{n=1}^{q} \sum_{\substack{\alpha_{1}, \dots, \alpha_{n} \in \mathbb{N}^{d} \setminus \{\mathbf{0}\}: \\ |\alpha_{1}| + \dots + |\alpha_{n}| = q}} \left| \int_{\Gamma^{\star}} \widehat{D}_{z,\xi}^{(n)} \left(\frac{\partial^{\alpha_{1}} \mathcal{H}_{\xi}}{\partial \xi_{\alpha_{1}}} \right)_{\ell_{0}k_{0},ab} e^{i\xi \cdot r_{\ell k}} d\xi \right|
$$

\n
$$
\leq \frac{C}{r_{\ell k}^{q}} \sum_{n=1}^{q} \sum_{\substack{\alpha_{1}, \dots, \alpha_{n} \in \mathbb{N}^{d} \setminus \{\mathbf{0}\}: \\ |\alpha_{1}| + \dots + |\alpha_{n}| = q}} \left(\mathfrak{d}^{\text{ref}} \right)^{-(n+1)} e^{-\gamma_{\text{CT}}(\mathfrak{d}^{\text{ref}}) r_{\ell k}}
$$

\n
$$
\leq \frac{Cq!}{r_{\ell k}^{q}} \left((\mathfrak{d}^{\text{ref}})^{-2} + (\mathfrak{d}^{\text{ref}})^{-3} + \dots + (\mathfrak{d}^{\text{ref}})^{-(q+1)} \right) e^{-\gamma_{\text{CT}}(\mathfrak{d}^{\text{ref}}) r_{\ell k}}
$$

\n
$$
\leq \frac{C_{q}(\mathfrak{d}^{\text{ref}})}{r_{\ell k}^{q}} e^{-\gamma_{\text{CT}}(\mathfrak{d}^{\text{ref}}) r_{\ell k}}, \tag{6.42}
$$

which completes the proof. \Box

Remark 6.5. The above result can be extended to $\mathcal{H}(u)$ using a similar argument as in Lemma [6.2](#page-14-1) by replacing the estimate for $|(z - H^{\text{ref}})_{\ell k, ab}^{-1}|$ with [\(6.31\)](#page-18-4), which yields

$$
\left| \left(z - \mathcal{H}(u) \right)^{-1}_{\ell k, ab} \right| \leq \frac{C_q(\mathfrak{d}^{\text{ref}})}{r_{\ell k}^q} e^{-\gamma_{\text{CT}}\left(\frac{1}{2}\mathfrak{d}^{\text{ref}}\right)r_{\ell k}} + C(u) e^{-\frac{1}{2}\gamma_{\text{CT}}\left(\frac{1}{2}\mathfrak{d}^{\text{ref}}\right)\left(|\ell| + |k|\right)},\tag{6.43}
$$

for all $\ell \neq k, \ell, k \in \Lambda$, and $1 \leq a, b \leq N_b$, where the constant $C(u)$ depends on $\mathfrak{d}(u)$ and $||Du||_{\ell^2_{\Upsilon}}$. □

We are now in a position to prove Proposition [3.9:](#page-7-4)

Proof of Proposition [3.9.](#page-7-4) For the inhomogeneous case, by using (6.43) , we have

$$
\begin{split}\n\left| \frac{\partial [\rho(u)]_{\ell\ell,ab}}{\partial [u(k)]_{i_1}} \right| &= \left| \oint_{\mathscr{C}} \left[(z - \mathcal{H}(u))^{-1} \frac{\partial \mathcal{H}(u)}{\partial [u(k)]_i} (z - \mathcal{H}(u))^{-1} \right]_{\ell\ell,ab} \frac{dz}{2\pi i} \right| \\
&\leq C \left| \left[(z - \mathcal{H}(u))^{-1} \frac{\partial [\mathcal{H}(u)]}{\partial [u(k)]_{i_1}} (z - \mathcal{H}(u))^{-1} \right]_{\ell\ell,ab} \right| \\
&\leq \sum_{m,n \in \Lambda} \left(\frac{C_q(\mathfrak{d}^{\text{ref}})}{(1 + r_{\ell m})^q} e^{-\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}}) r_{\ell m}} + C(u) e^{-\frac{1}{2}\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}})(|\ell| + |m|)} \right) e^{-\gamma_{0}\mathfrak{m}(r_{mk} + r_{kn})} \\
&\cdot \left(\frac{C_q(\mathfrak{d}^{\text{ref}})}{(1 + r_{n\ell})^q} e^{-\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}}) r_{n\ell}} + C(u) e^{-\frac{1}{2}\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}})(|n| + |\ell|)} \right) \\
&\leq \sum_{m \in \Lambda} \left[C_q(\mathfrak{d}^{\text{ref}}) \right]^2 \frac{e^{-2[\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}}) r_{\ell m} + \gamma_{0}\mathfrak{m} r_{mk}]}{(1 + r_{\ell m})^{2q}} + [C(u)]^2 \sum_{m \in \Lambda} e^{-[\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}})(|\ell| + |m|) + 2\gamma_{0}\mathfrak{m} r_{mk}]} \\
&\quad + C(u) C_q(\mathfrak{d}^{\text{ref}}) \sum_{m \in \Lambda} \frac{e^{-[\gamma_{\text{CT}}(\frac{1}{2}\mathfrak{d}^{\text{ref}}) r_{\ell m} + \gamma_{0}\mathfrak{m} r_{mk
$$

Note that the following estimates: for fixed $\ell, k \in \Lambda, \gamma \geq \beta > 0$, we have

$$
\sum_{m\in\Lambda} \frac{e^{-(\beta r_{\ell m} + \gamma r_{mk})}}{(1+r_{\ell m})^q} \leq \sum_{m\in\Lambda} \frac{e^{-(\frac{\beta}{2}r_{\ell k} + \frac{\gamma}{2}r_{mk})}}{(1+|r_{\ell k}-r_{mk}|)^q} \n\leq Ce^{-\frac{\beta}{2}r_{\ell k}} \left(\int_0^{r_{\ell k}} \frac{e^{-\frac{\gamma}{2}r}r^{d-1}}{(1+|r_{\ell k}-r|)^q} dr + \int_{r_{\ell k}}^{\infty} \frac{e^{-\frac{\gamma}{2}r}r^{d-1}}{(1+|r_{\ell k}-r|)^q} dr \right) \n\leq Ce^{-\beta r_{\ell k}} \left(-\int_0^{r_{\ell k}} \frac{e^{\frac{\gamma}{2}r}(r_{\ell k}-r)^{d-1}}{(1+r)^q} dr + \int_0^{\infty} \frac{e^{-\frac{\gamma}{2}r}(r_{\ell k}+r)^{d-1}}{(1+r)^q} dr \right) \n\leq C \frac{e^{-\beta r_{\ell k}}}{(1+r_{\ell k})^q},
$$
\n(6.45)

and

$$
\sum_{m \in \Lambda} e^{-(\beta|m| + \gamma r_{mk})} \le e^{-\frac{\beta}{2}|k|} \left(\sum_{m \in \Lambda} e^{-\frac{\gamma}{2}r_{mk}} \right) \le C e^{-\frac{\beta}{2}|k|},\tag{6.46}
$$

for some constant $C > 0$ depending on d, \mathfrak{m}, γ , then we can bound [\(6.44\)](#page-20-1) by

$$
\left| \frac{\partial [\rho(u)]_{\ell\ell,ab}}{\partial [u(k)]_{i_1}} \right| \leq \frac{C_q^2 (\text{gap}_-)}{(1+r_{\ell k})^{2q}} e^{-2\eta-r_{\ell k}} + [C(u)]^2 e^{-2\eta}-(|\ell|+|k|) + \frac{C(u)C_q (\text{gap}_-)}{(1+r_{\ell k})^q} e^{-\eta}-(|\ell|+|k|+r_{\ell k})
$$

$$
\leq \left[\frac{C_q (\text{gap}_-)}{(1+r_{\ell k})^q} + C(u) \right]^2 e^{-2\eta-r_{\ell k}},
$$

which completes the proof. \Box

Appendix A. Bloch Transform for the Tight Binding Hamiltonian

Recall that Γ, Γ^* are unit cells of Λ and the corresponding reciprocal lattice, respectively. Let us denote all the lattice sites in the unit cell by $\Lambda_0 = \Gamma \cap \Lambda$, and denote the set of orbitals by Ξ.

Given an atom site $k \in \Lambda$, there exits a vector $\alpha_k \in \mathbb{Z}^d$ such that $k = k_0 + \mathsf{A}\alpha_k$, $k_0 \in \Lambda_0$. Then, we define the operator $U: \ell^2(\Lambda \times \Xi) \to L^2(\Gamma^*, \ell^2(\Lambda_0 \times \Xi))$ as

$$
(U\psi)_{\xi}(k; a) := \hat{\psi}_{\xi}(k_0; a) = \sum_{\alpha \in \mathbb{Z}^d} \psi(k_0 + A\alpha; a) e^{-i\xi \cdot (k_0 + A\alpha)},
$$

where $\xi \in \Gamma^*, k_0 \in \Lambda_0$, and $1 \le a \le N_b$. The space $L^2(\Gamma^*, \ell^2(\Lambda_0 \times \Xi))$ is a Hilbert space endowed with the inner product

$$
\langle \hat{\psi}, \hat{\phi} \rangle_{L^2(\Gamma^*, \ell^2(\Lambda_0 \times \Xi))} := \int_{\Gamma^*} \langle \hat{\psi}_{\xi}(\cdot), \hat{\phi}_{\xi}(\cdot) \rangle_{\ell^2(\Lambda_0 \times \Xi)} d\xi = \sum_{k_0 \in \Lambda_0, a \in \Xi} \int_{\Gamma^*} \hat{\psi}_{\xi}^*(k_0; a) \hat{\phi}_{\xi}(k_0; a) d\xi.
$$

It is straightforward to verify that U is an isometry with inverse $U^* : L^2(\Gamma^*, \ell^2(\Lambda_0 \times \Xi)) \to$ $\ell^2(\Lambda \times \Xi)$ defined by

$$
(U^*\hat{\psi}_{\boldsymbol{\xi}})(k_0+\mathsf{A}\alpha):=\int_{\Gamma^*}\hat{\psi}_{\boldsymbol{\xi}}(k_0;a)e^{i\boldsymbol{\xi}\cdot(k_0+\mathsf{A}\alpha)}\,\mathrm{d}\boldsymbol{\xi},
$$

for $k_0 \in \Lambda_0$ and $\alpha \in \mathbb{Z}^d$.

The reference Hamiltonian \mathcal{H}^{ref} we defined in [\(2.6\)](#page-2-2) is a linear self-adjoint operator on $\ell^2(\Lambda \times$ Ξ). Following [\[12,](#page-23-15) [32\]](#page-24-8), there exits a direct integral decomposition of Href given by

$$
U\mathcal{H}^{\text{ref}}U^* = \int_{\Gamma^*}^{\oplus} \mathcal{H}_{\xi} \,\mathrm{d}\xi,
$$

where $f_{\Gamma^*}^{\oplus}$ denotes the direct integral and \mathcal{H}_{ξ} satisfies $(U\mathcal{H}^{\text{ref}}\psi)_{\xi} = \mathcal{H}_{\xi}\hat{\psi}_{\xi}$ for almost every $\xi \in \Gamma^*$. Besides, we have

$$
[\mathcal{H}_{\xi}]^{ab}_{\ell_0 k_0} \coloneqq \sum_{\alpha \in \mathbb{Z}^d} [\mathcal{H}^{\text{ref}}]^{ab}_{\ell_0 + \mathsf{A}\alpha, k_0} e^{-i\xi \cdot (\ell_0 - k_0 + \mathsf{A}\alpha)} \qquad \forall \xi \in \Gamma^*, \ \ell_0, k_0 \in \Lambda_0,
$$

where \mathcal{H}_{ξ} is a $MN_{\text{b}} \times MN_{\text{b}}$ matrix.

For any $\xi \in \Gamma^*$, by solving the eigenvalue problem

$$
\mathcal{H}_{\xi}u_n(\xi) = \varepsilon_n(\xi)u_n(\xi), \quad n = 1, \dots, MN_b,
$$
\n(A.1)

we get the spectrum $\{\varepsilon_n(\boldsymbol{\xi})\}_{n=1}^{MN_b}$, where the ordered eigenvalues $\varepsilon_1(\boldsymbol{\xi}) \leq \cdots \leq \varepsilon_{MN_b}(\boldsymbol{\xi})$ are continuous on Γ^* [\[8,](#page-23-22) [21\]](#page-23-23). Finally, we obtain the band structure:

$$
\sigma(\mathcal{H}^{\text{ref}}) = \bigcup_{j=1}^{MN_{\text{b}}} \left\{ \varepsilon_n(\boldsymbol{\xi}) : \boldsymbol{\xi} \in \Gamma^* \right\}.
$$

Appendix B. Computational Details in 1D Chain

Here we will provide the computational details of 1D chain tests. Applying Bloch transform for the Hamiltonian in [\(4.1\)](#page-8-2) yields that

$$
\mathcal{H}_{\xi} = \begin{pmatrix} c_1 + 2f_1(1)\cos(\xi) & 2f_3(1)\cos(\xi) \\ 2f_3(1)\cos(\xi) & c_2 + 2f_2(1)\cos(\xi) \end{pmatrix}, \quad \forall \xi \in \Gamma^* = [-\pi, \pi].
$$

For the eigenvalue problem $\mathcal{H}_{\xi}u_n(\xi) = \varepsilon_n(\xi)u_n(\xi)$, we solve it by considering the equation

det $\left|\varepsilon(\xi) - \mathcal{H}_{\xi}\right| = 0,$

we obtain the two energy bands $\{\varepsilon_n(\xi)\}_{n=1,2}$,

$$
\varepsilon_1(\xi) = \frac{a(\xi) + b(\xi)}{2} - \sqrt{\frac{(a(\xi) - b(\xi))^2}{4} + 4 (f_3(1)\cos(\xi))^2}
$$

$$
\varepsilon_2(\xi) = \frac{a(\xi) + b(\xi)}{2} + \sqrt{\frac{(a(\xi) - b(\xi))^2}{4} + 4 (f_3(1)\cos(\xi))^2}
$$

where we denote $a(\xi) := c_1 + 2f_1(1)\cos(\xi)$ and $b(\xi) := c_2 + 2f_2(1)\cos(\xi)$. Then gap_+ can be given immediately by

$$
\mathsf{gap}_{+} = \min_{\xi \in \Gamma^{*}} (\varepsilon_{2}(\xi) - \varepsilon_{1}(\xi)) = \min_{\xi \in \Gamma^{*}} 2\sqrt{\frac{(a(\xi) - b(\xi))^{2}}{4} + 4\left(f_{3}(1)\cos(\xi)\right)^{2}}
$$

$$
= \frac{2f_{3}(1)|c_{1} - c_{2}|}{\sqrt{\left(f_{1}(1) - f_{2}(1)\right)^{2} + \left(2f_{3}(1)\right)^{2}}}.
$$
(B.1)

By adjusting $f_1(1)$, $f_2(1)$, $f_3(1)$, c_1 , c_2 , we can get systems with fixed gap_+ but different gap_- .

Remark B.1. There exits other possible expression for gap_{+} :

$$
\mathsf{gap}_{+} = [c_1 - c_2 \pm 2(f_1(1) - f_2(1))]^2 + 16f_3(1)^2,
$$

as the minima of $(\varepsilon_2(\xi)-\varepsilon_1(\xi))$ occur at 0 or $\pm\pi$. However, in our tests, the chosen parameters yield gap_+ as defined by [\(B.1\)](#page-22-1).

Appendix C. Exponential Sums

Throughout Section [6,](#page-12-2) we frequently apply estimates for exponential sums. For the convenience of the reader, we present these elementary estimates here.

Lemma C.1. For $\gamma > \eta > 0$, $\ell, k \in \Lambda$, and $A \subseteq \Lambda$,

$$
\sum_{m \in A} e^{-\gamma r_{\ell m}} e^{-\eta r_{mk}} \le \left[1 + \frac{C_d}{(\mathfrak{m}\gamma)^d} \right] e^{-\frac{1}{2} \frac{\min}{m \in A} [\gamma r_{\ell m} + \eta r_{mk}]} \tag{C.1}
$$

$$
\leq \left[1 + \frac{C_d}{(\mathfrak{m}\gamma)^d}\right] e^{\gamma \sup_{a \in A} |a|} e^{-\frac{1}{2}(\gamma|\ell| + \eta|k|)} \tag{C.2}
$$

for some C_d depending only on d.

We apply Lemma [C.1](#page-22-0) with $A = \Lambda$ and replace the exponent in the first line with $\eta r_{\ell k} \leq$ $\min_{m \in \Lambda} [\gamma r_{\ell m} + \eta r_{m k}]$. When $A = \Lambda \cap B_R$, we may apply the second line with $\sup_{a \in A} |a| = R$. a∈A

Proof. Here, we follow [\[34\]](#page-24-9). Since $\gamma r_{\ell m} + \eta r_{mk} \ge \min_{m \in A} [\gamma r_{\ell m} + \eta r_{mk}]$ and $\gamma r_{\ell m} + \eta r_{mk} \ge \gamma r_{\ell m}$, we have

$$
\sum_{m \in A} e^{-\gamma r_{\ell m}} e^{-\eta r_{mk}} \le \left(\sum_{m \in A} e^{-\frac{1}{2}\gamma r_{\ell m}}\right) e^{-\frac{1}{2} \min_{m \in A} \left[\gamma r_{\ell m} + \eta r_{mk}\right]}.
$$
\n(C.3)

Additionally, by noting that $e^{-\gamma r_{\ell m}} \leq e^{-\gamma |\bm{r}-\bm{r}_{\ell}|}$ for all $\bm{r} \in B_{r_{\ell m}}(\bm{r}_{\ell})$, and the non-interpenetration condition in (2.5) , we can approximate eq. $(C.3)$ with the following integral

$$
\sum_{m\neq\ell} e^{-\frac{1}{2}\gamma r_{\ell m}} \leq \sum_{m\neq\ell} \oint_{B_{r_{\ell m}}(r_{\ell})\cap B_{m/2}(r_m)} e^{-\frac{1}{2}\gamma |r-r_{\ell}|} dr \leq \frac{C_d}{\mathfrak{m}^d} \int_{\mathbb{R}^d} e^{-\frac{1}{2}\gamma |r-r_{\ell}|} dr
$$

$$
= \frac{C_d}{\mathfrak{m}^d} \int_0^\infty e^{-\frac{1}{2}\gamma r} r^{d-1} dr = \frac{C_d}{(\mathfrak{m}\gamma)^d},
$$

where the constant C_d changes from one line to the next. Together with $(C.3)$, this concludes the proof of $(C.1)$. We conclude $(C.2)$ by noting that

$$
\frac{1}{2} \min_{m \in A} [\gamma r_{\ell m} + \eta r_{mk}] \ge \frac{1}{2} [\gamma \text{dist}(\ell, A) + \eta \text{dist}(k, A)]
$$

$$
\ge \frac{1}{2} (\gamma |\ell| + \eta |k|) - \gamma \sup_{a \in A} |a|.
$$

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